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(19) **United States**(12) **Patent Application Publication****Kurokawa et al.**(10) **Pub. No.: US 2017/0046002 A1**(43) **Pub. Date: Feb. 16, 2017**(54) **INPUT-OUTPUT DEVICE AND METHOD
FOR DRIVING INPUT-OUTPUT DEVICE****Publication Classification**(71) Applicant: **Semiconductor Energy Laboratory
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Co., Ltd., Kanagawa-ken (JP)**(21) Appl. No.: **15/340,562**(22) Filed: **Nov. 1, 2016****Related U.S. Application Data**(63) Continuation of application No. 13/160,903, filed on
Jun. 15, 2011, now Pat. No. 9,489,088.(30) **Foreign Application Priority Data**

Jun. 16, 2010 (JP) 2010-137090

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(2013.01); **G06F 3/0421** (2013.01)

(57)

ABSTRACT

Accuracy of photodetection is improved. An input-output device includes a light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range and a second light-emitting diode that emits light with a wavelength in an infrared range; a display circuit that is supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal is input, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal.

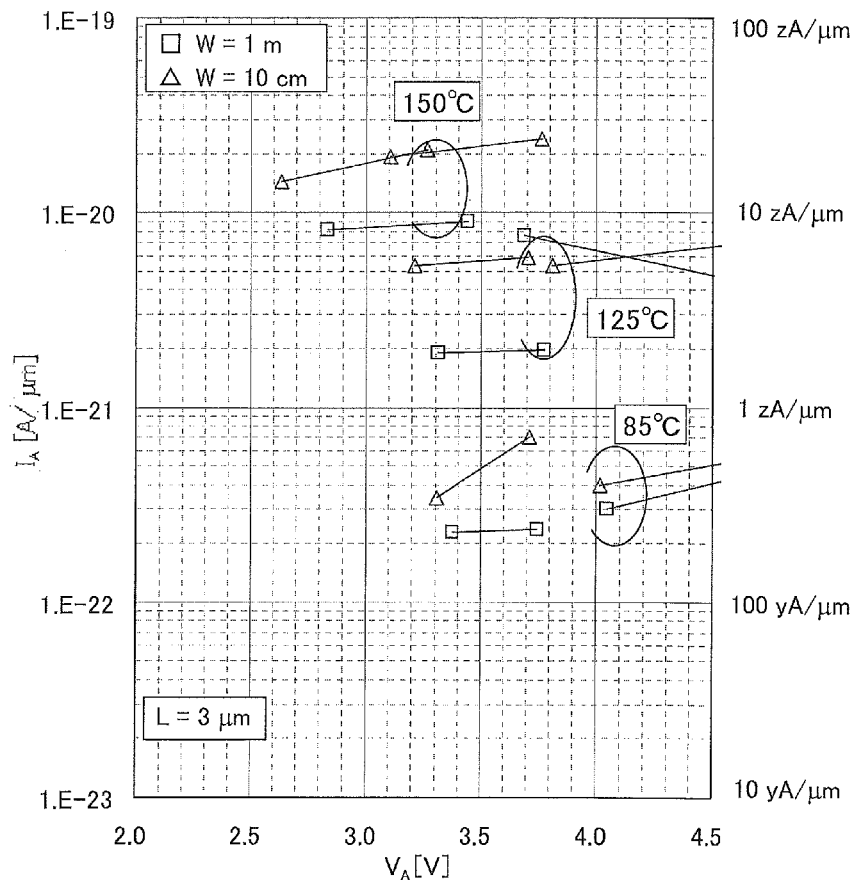


FIG. 1A

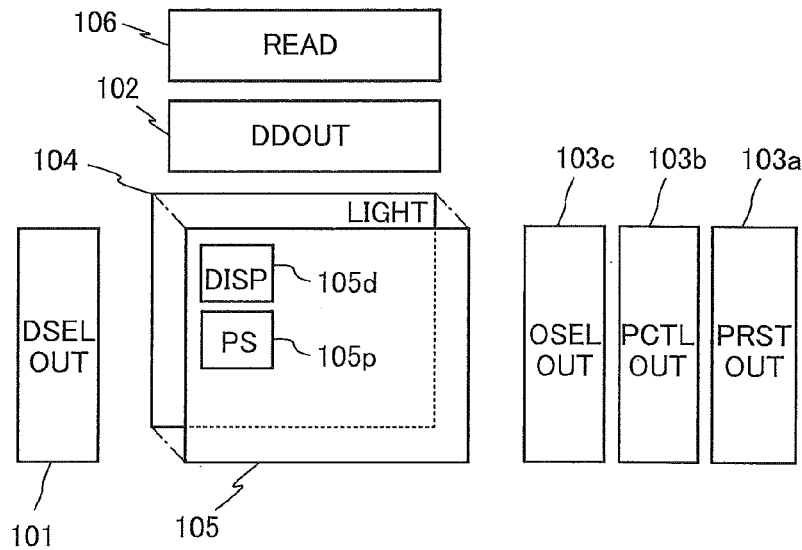


FIG. 1B

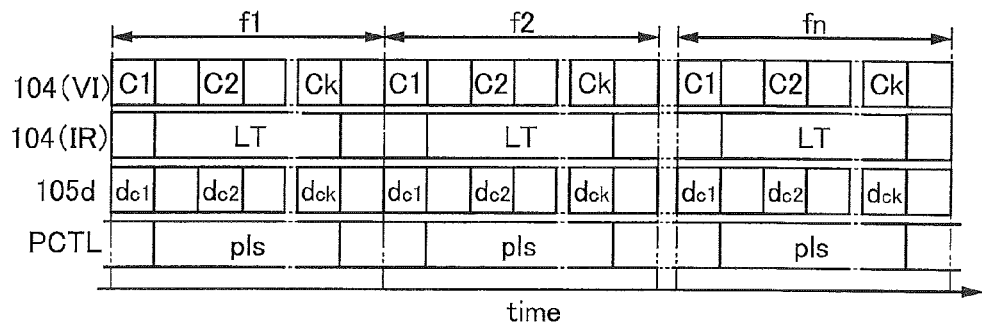


FIG. 2A

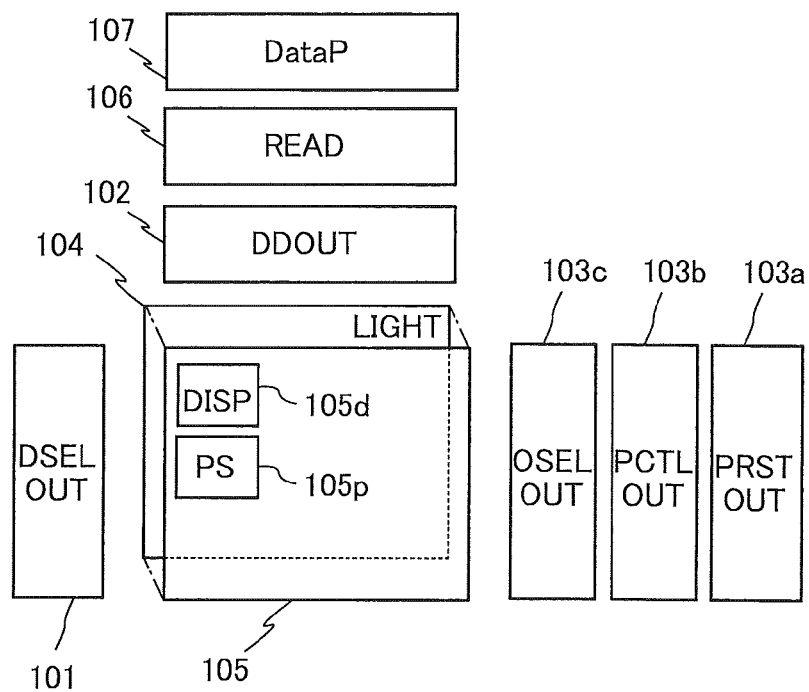


FIG. 2B

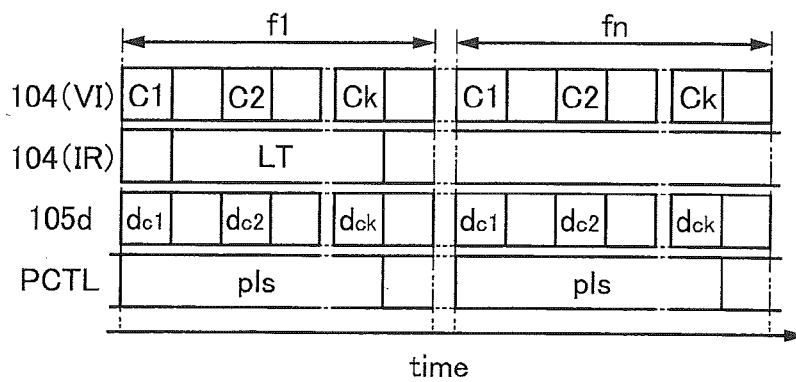


FIG. 3A

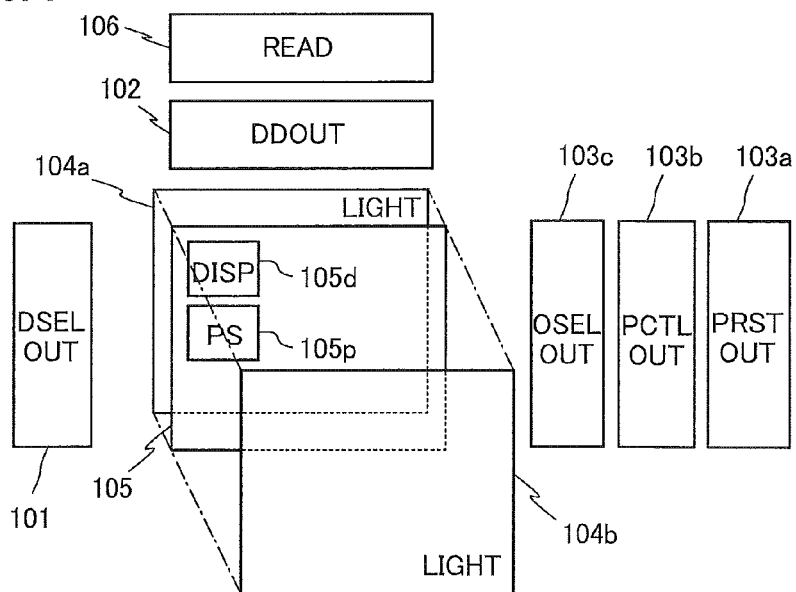


FIG. 3B

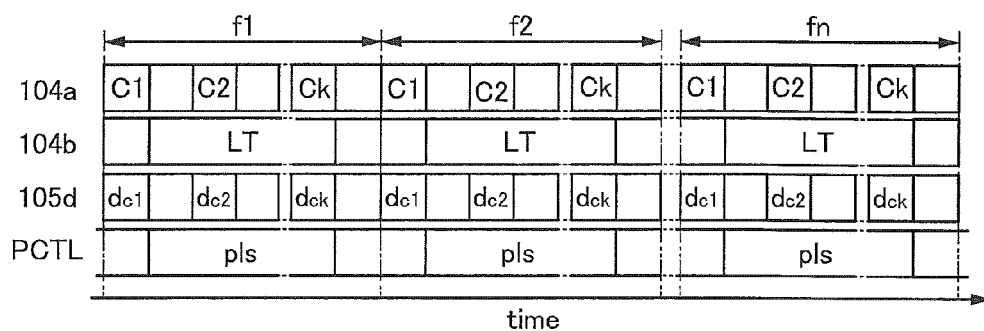


FIG. 4A

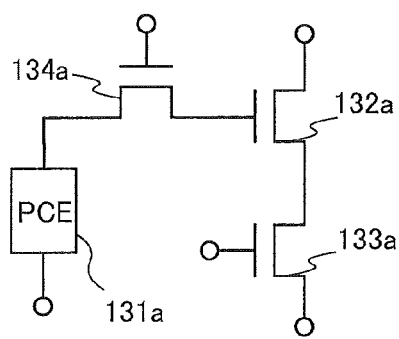


FIG. 4C

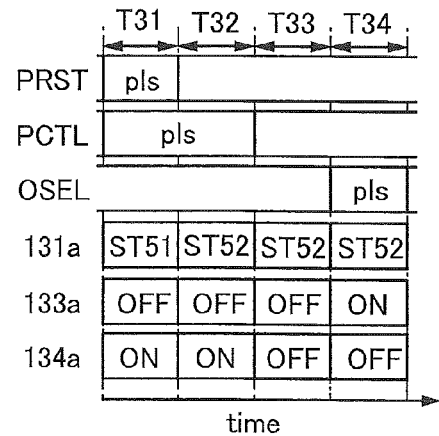


FIG. 4B

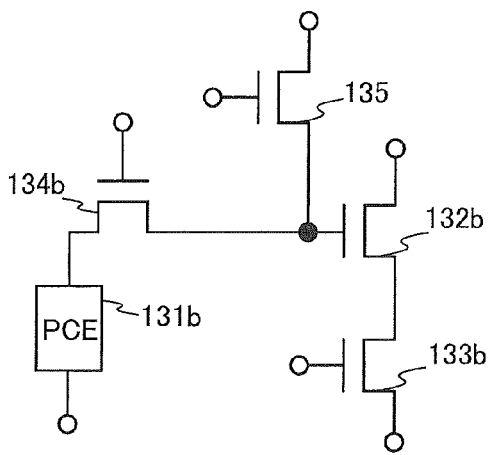


FIG. 4D

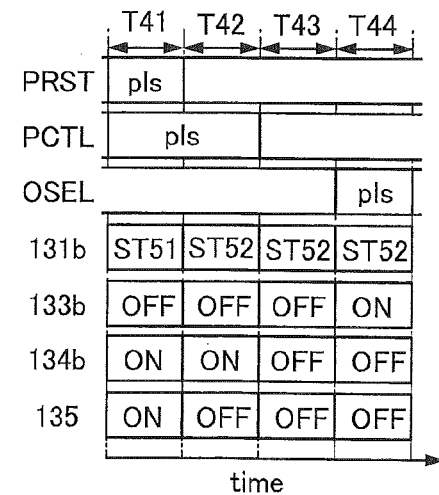


FIG. 5A

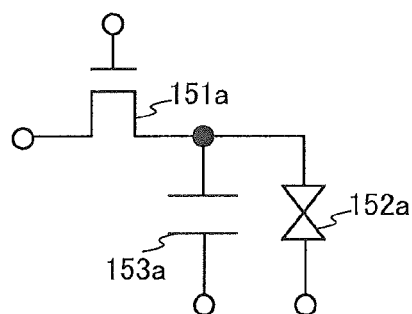


FIG. 5C

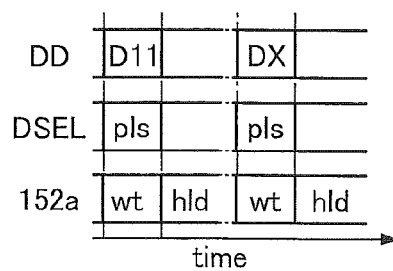


FIG. 5B

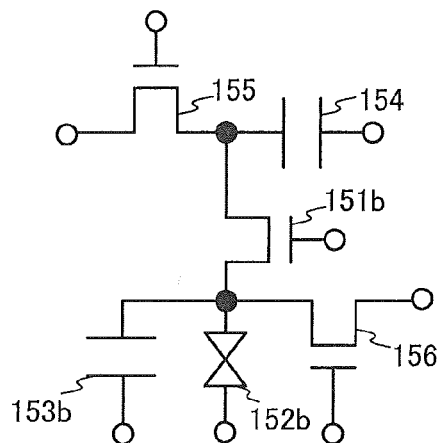


FIG. 5D

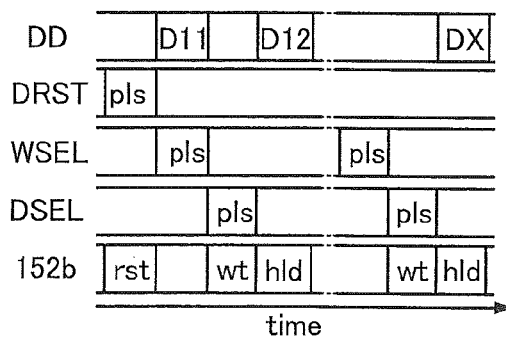


FIG. 6

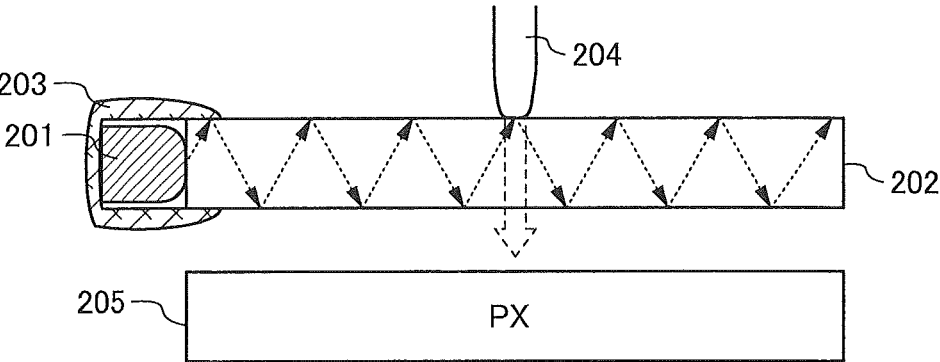


FIG. 7A

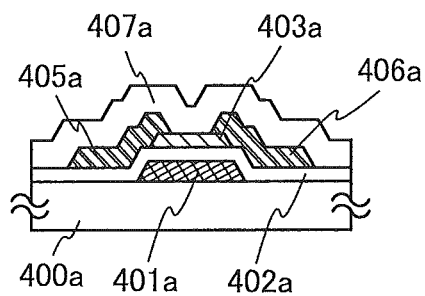


FIG. 7B

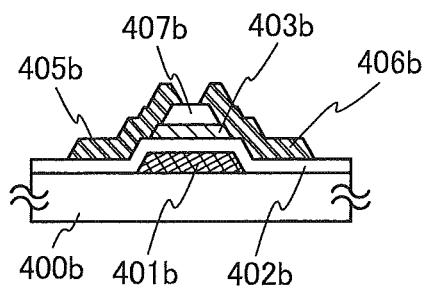


FIG. 7C

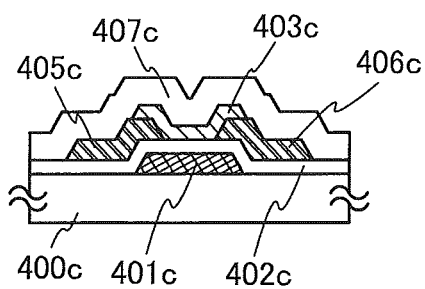


FIG. 7D

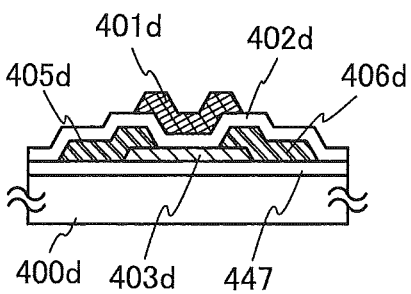


FIG. 8A

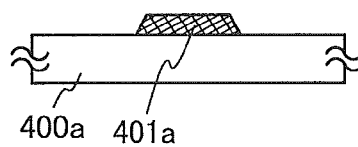


FIG. 8B

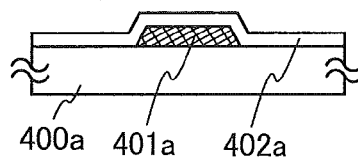


FIG. 8C

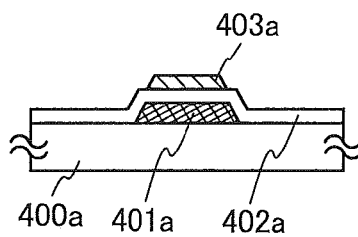


FIG. 8D

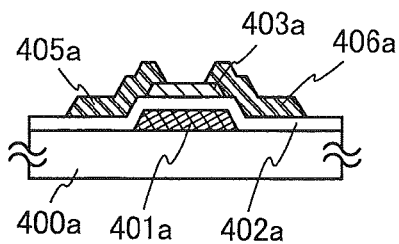


FIG. 8E

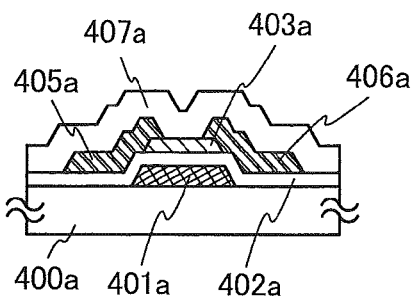


FIG. 9A

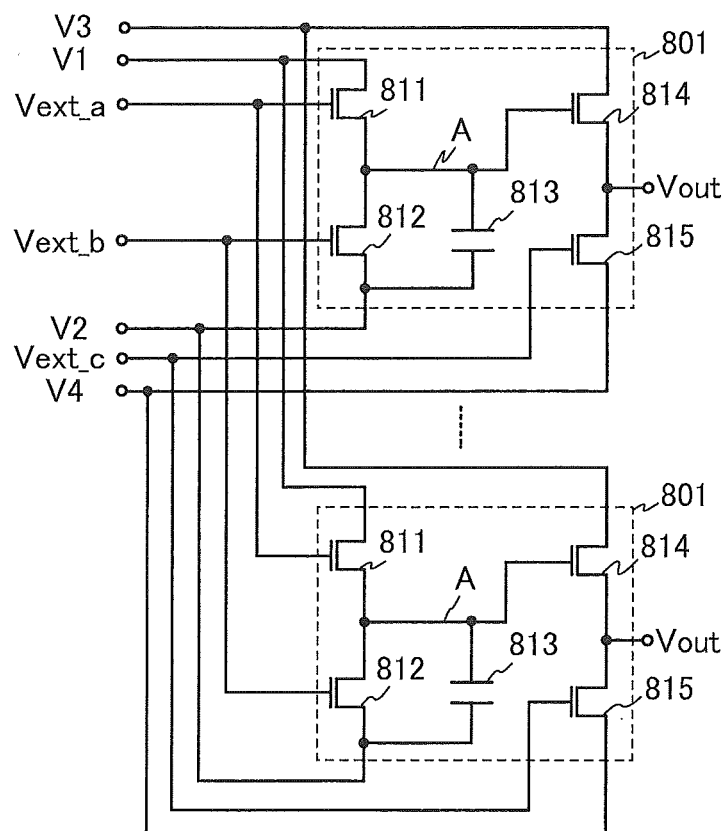


FIG. 9B

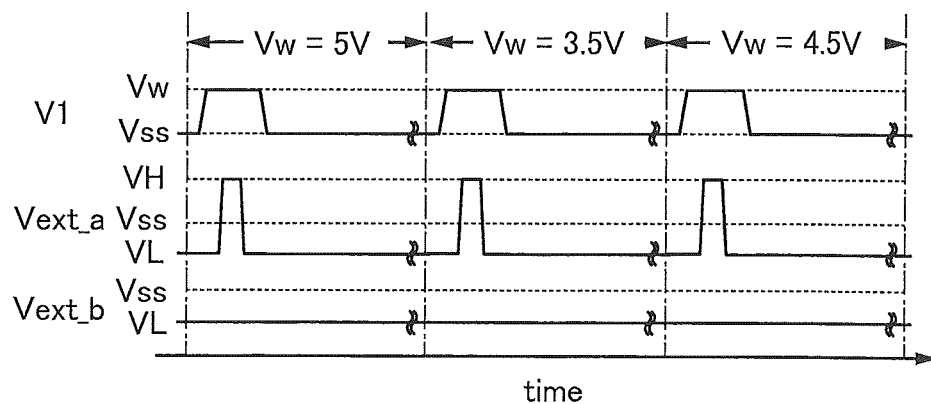


FIG. 10A

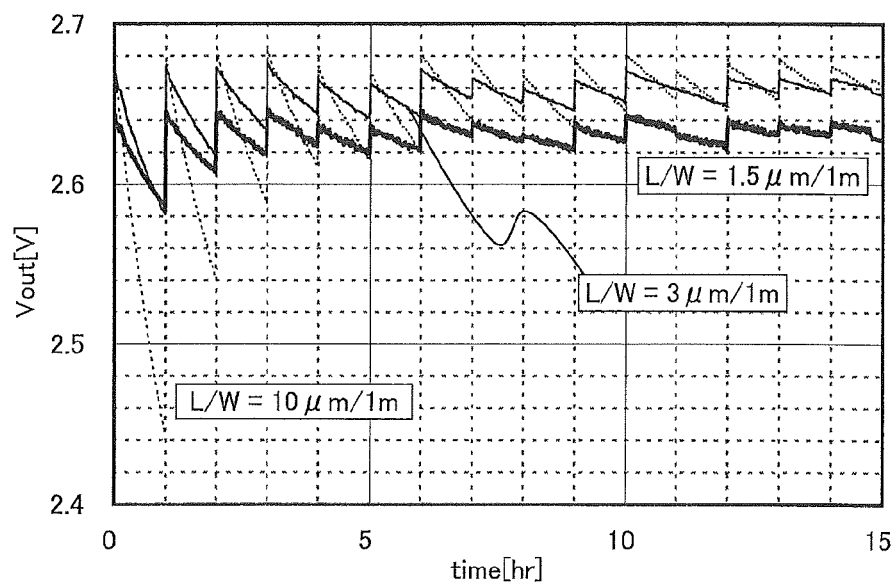


FIG. 10B

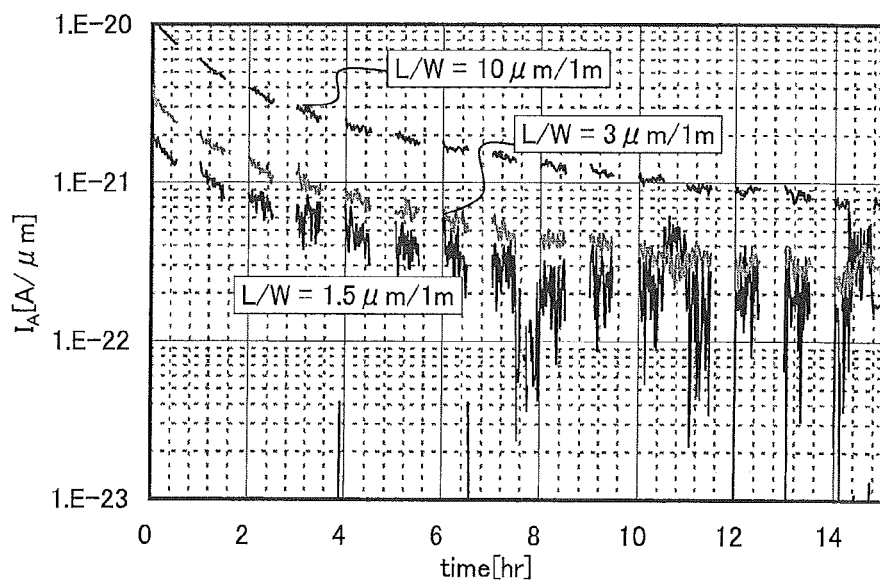


FIG. 11

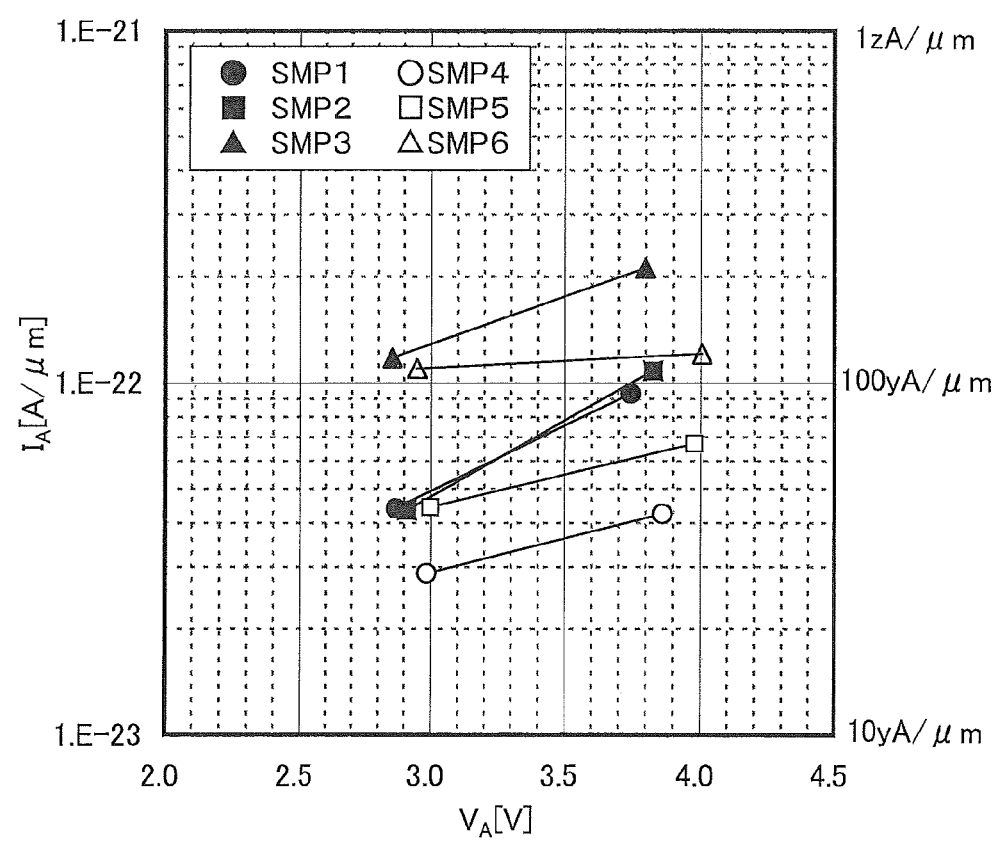


FIG. 12

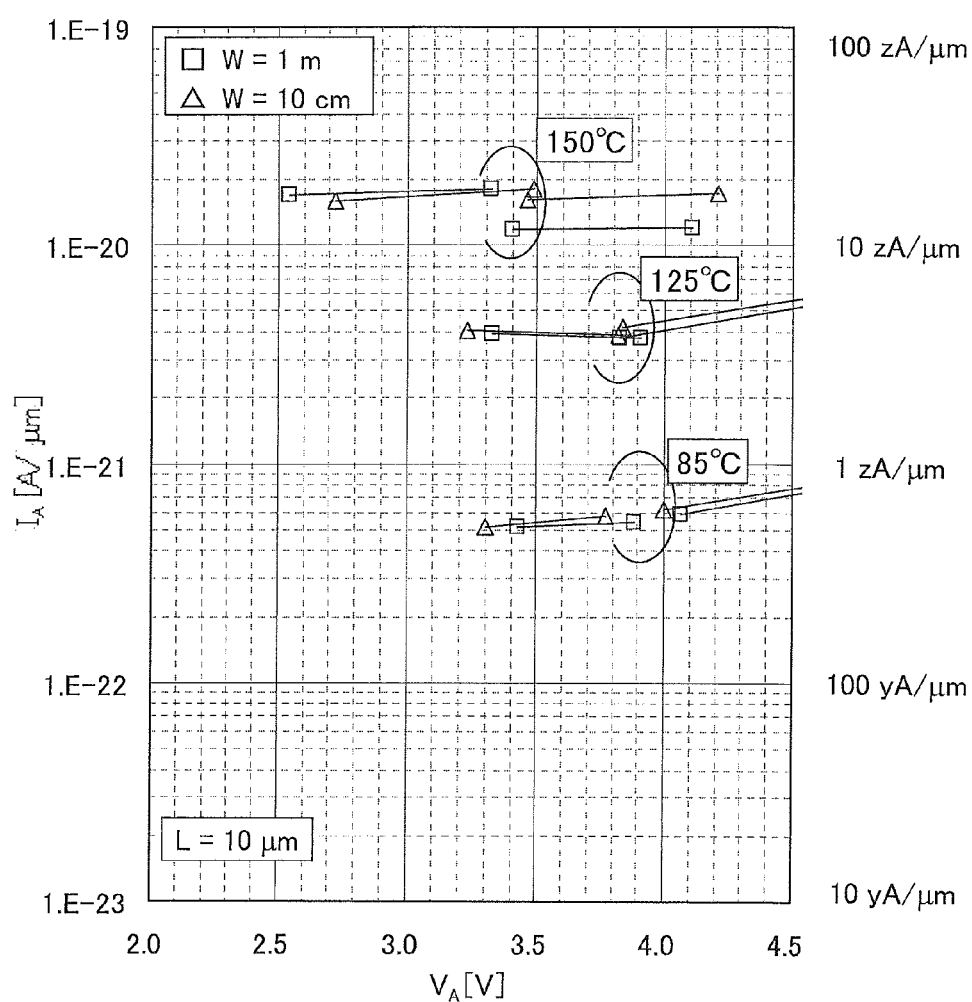


FIG. 13

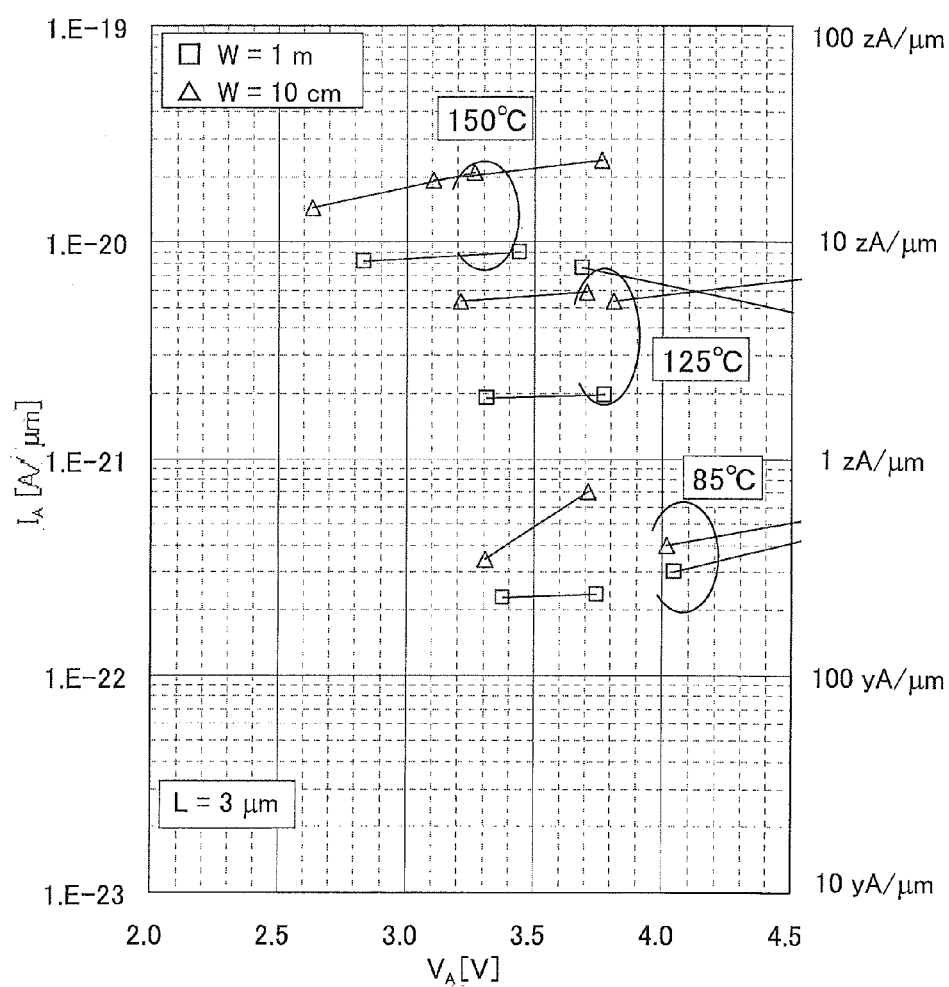


FIG. 14

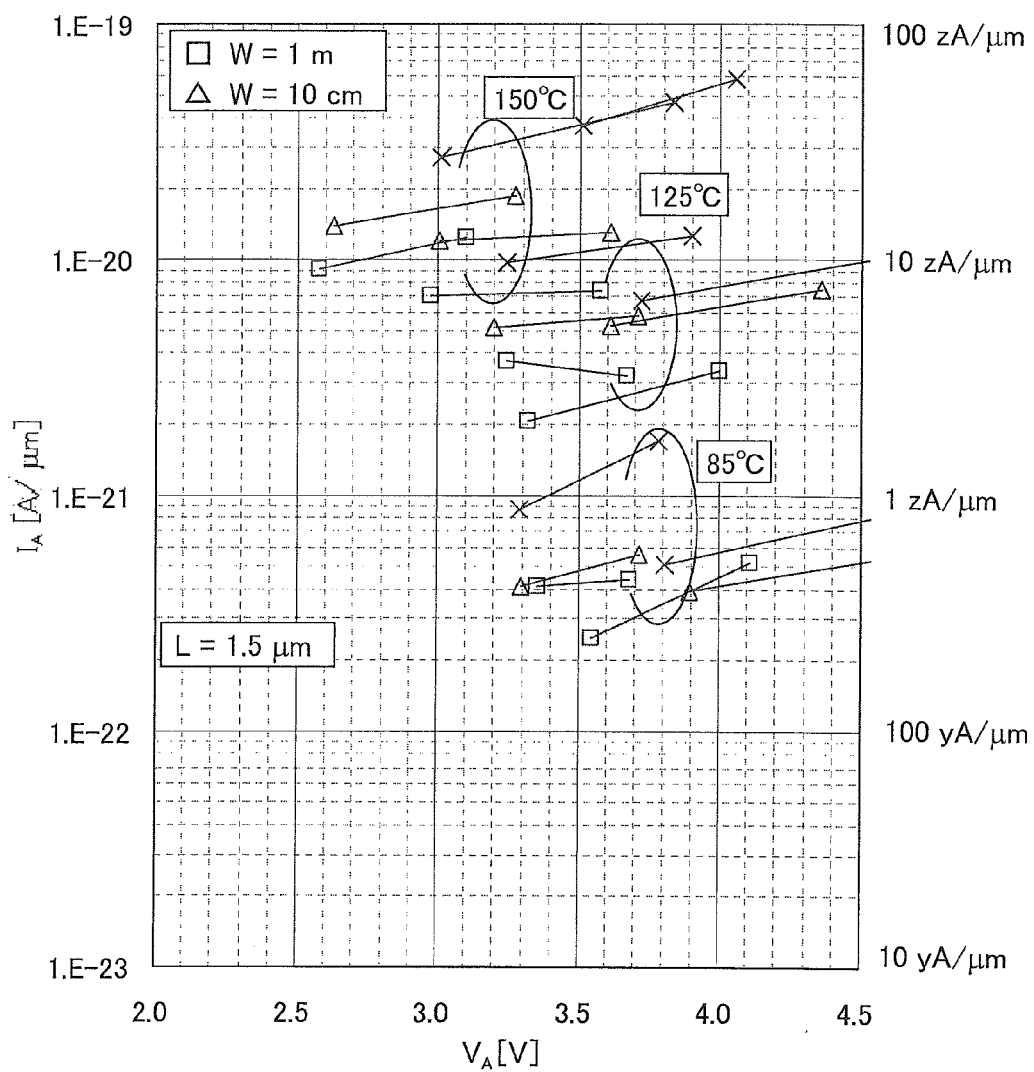


FIG. 15A

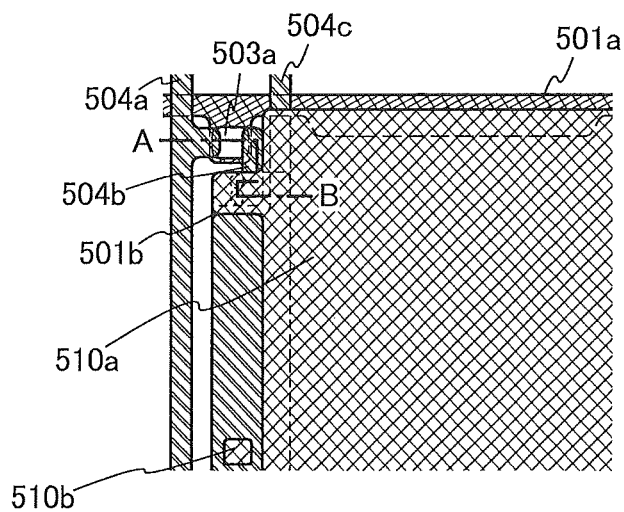


FIG. 15B

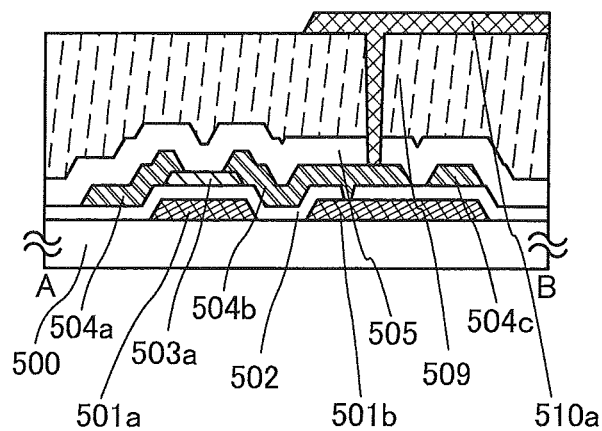


FIG. 16A

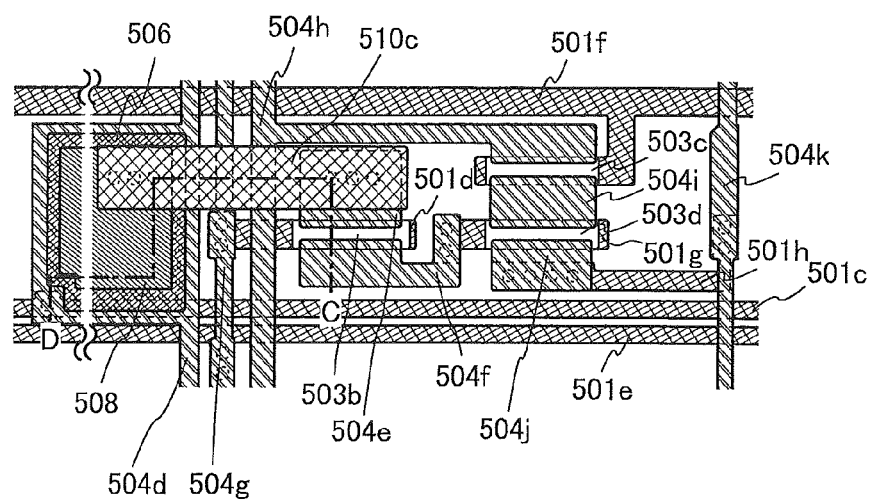


FIG. 16B

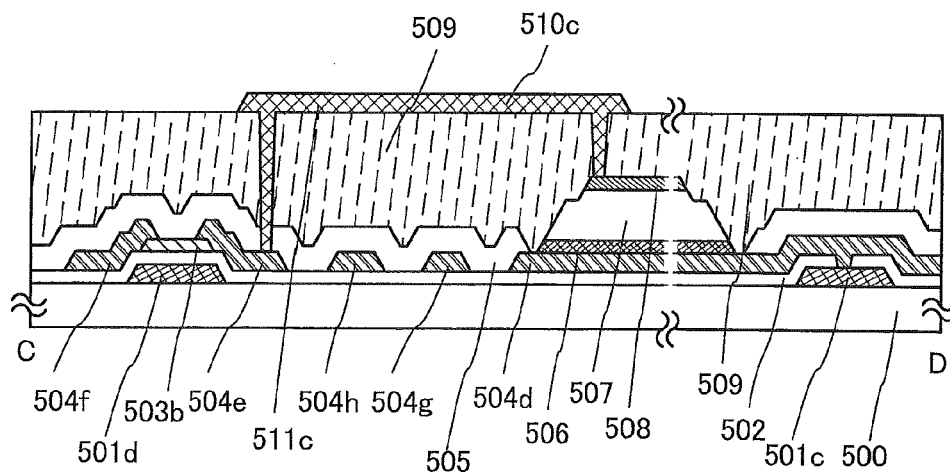


FIG. 17A

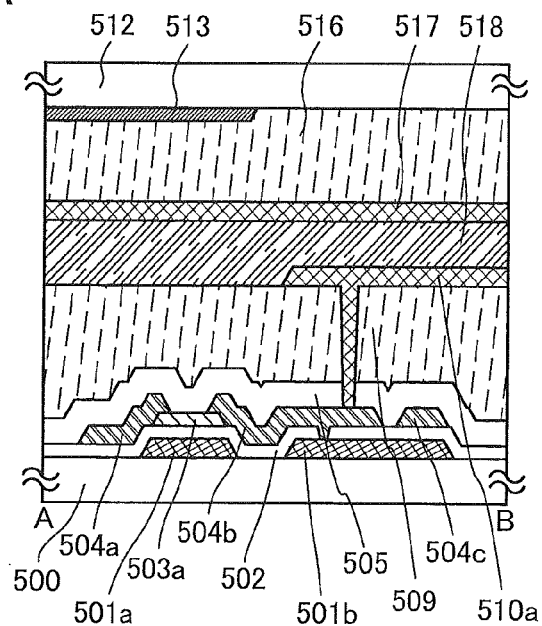


FIG. 17B

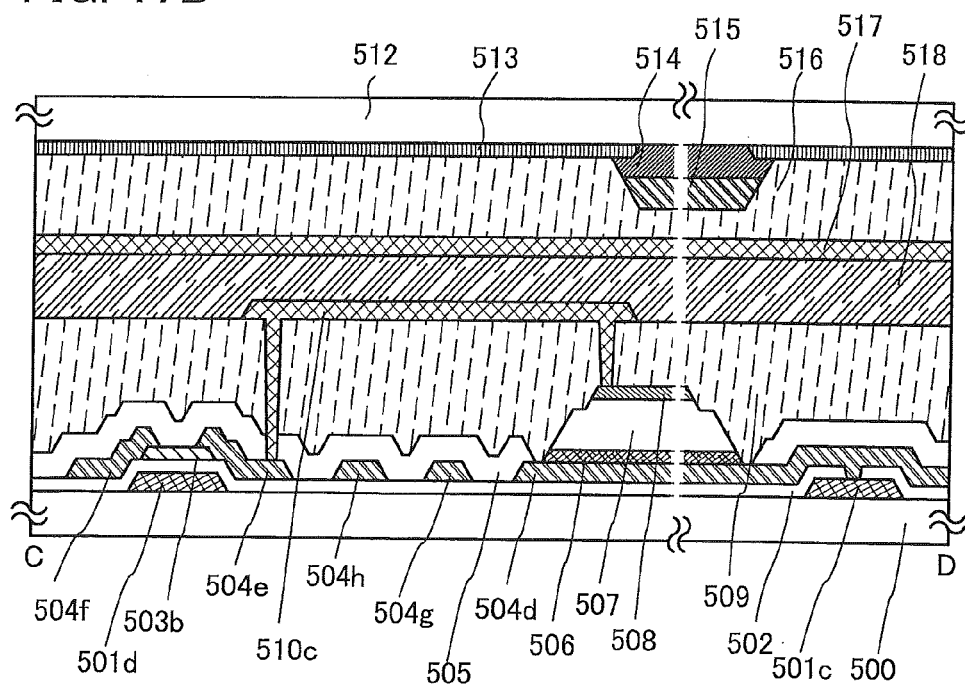


FIG. 18A

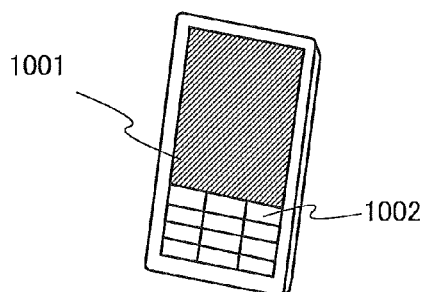


FIG. 18D

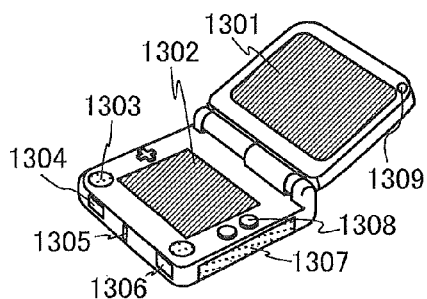


FIG. 18B

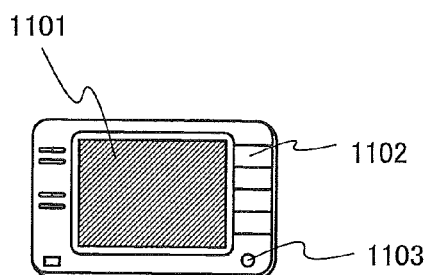


FIG. 18E

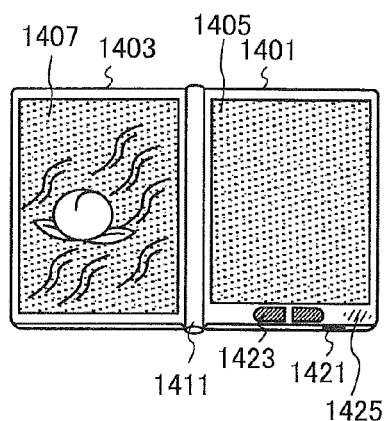


FIG. 18C

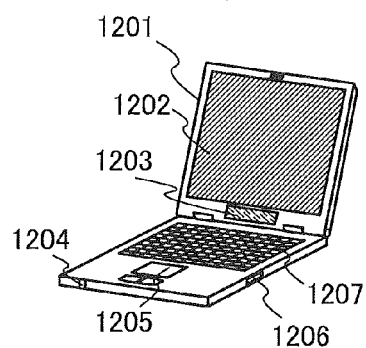
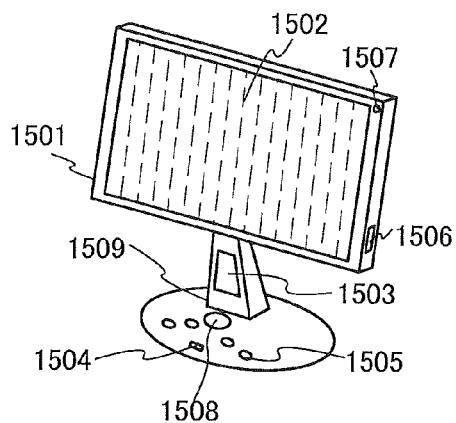


FIG. 18F



INPUT-OUTPUT DEVICE AND METHOD FOR DRIVING INPUT-OUTPUT DEVICE

[0001] This application is a continuation of copending U.S. application Ser. No. 13/160,903, filed on Jun. 15, 2011 which is incorporated herein by reference.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] One embodiment of the present invention relates to an input-output device.

[0004] Further, one embodiment of the present invention relates to a method for driving an input-output device.

[0005] 2. Description of the Related Art

[0006] In recent years, techniques of devices from which data is output and to which data is input by incidence of light (such devices are also referred to as input-output devices) have been developed.

[0007] As an input-output device, there is an input-output device which includes a plurality of photodetectors (also referred to as optical sensors) arranged in matrix in a pixel portion and a backlight including light-emitting diodes with a plurality of colors as light sources (for example, Reference 1). In the input-output device disclosed in Reference 1, in each frame period, the backlight is lit while the colors of emitted light are switched so that full-color images are displayed, and light reflected by an object is read as data. Thus, the input-output device disclosed in Reference 1 functions as a touch panel. Note that a method by which a backlight is lit while the colors of emitted light are switched in each frame period is also referred to as a field-sequential method.

REFERENCE

[0008] Reference 1: Japanese Published Patent Application No. 11-008741

SUMMARY OF THE INVENTION

[0009] A conventional input-output device has a problem of low accuracy of photodetection.

[0010] For example, when the conventional input-output device employs a field-sequential method, it is necessary that a plurality of light-emitting diodes be sequentially switched and emit light in one frame period so that the lighting state of a backlight can be switched. Thus, in order to generate optical data based on the lighting state of the backlight, it is necessary that optical data be generated in the photodetector in each row so that optical data can be generated in all the photodetectors in a period during which the backlight is lit. Accordingly, the light incidence time in each photodetector at the time of generating optical data is short, so that accuracy of photodetection is reduced.

[0011] In addition, for example, light in an environment in which an input-output device is placed, such as external light, enters the input-output device. Thus, the light in the environment causes noise when optical data is generated. Accordingly, accuracy of photodetection is reduced. For example, as in a touch panel, in the case where data is input to the input-output device by entry of light reflected by a finger, light reflected by a hand portion other than the finger is recognized as data equivalent to data brought by the light reflected by the finger in some cases due to light in the environment in which the input-output device is placed.

[0012] An object of one embodiment of the present invention is to improve accuracy of photodetection.

[0013] One embodiment of the present invention includes a display circuit, a plurality of photodetectors, and a light unit including a plurality of first light-emitting diodes that emit visible light and a second light-emitting diode that emits infrared light. The plurality of first light-emitting diodes are switched and emit light per unit time and the second light-emitting diode emits light, so that optical data is generated in the plurality of photodetectors. Thus, the influence of light in an environment in which an input-output device is placed is reduced.

[0014] One embodiment of the present invention is an input-output device which includes a light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range and a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits overlapping with the light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors overlapping with the light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal.

[0015] One embodiment of the present invention is an input-output device which includes a first light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range; a second light unit including a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits provided between the first light unit and the second light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors provided between the first light unit and the second light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal.

[0016] One embodiment of the present invention is a method for driving an input-output device which includes a light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range and a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits overlapping with the light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors overlapping with the light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal. In the method, in a frame period set by the display selection signal, a first region in the light unit is lit while the

Z first light-emitting diodes are sequentially switched and emit light, and a second region in the light unit is lit while the second light-emitting diode emit light. Y pieces of data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second region in the light unit is lit.

[0017] One embodiment of the present invention is a method for driving an input-output device which includes a light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range and a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits overlapping with the light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors overlapping with the light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal. In the method, in a frame period set by the display selection signal, a first region in the light unit is lit while the Z first light-emitting diodes are sequentially switched and emit light, and a second region in the light unit is lit while the second light-emitting diode emit light. Y pieces of first data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second region in the light unit is lit, and Y pieces of second data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second region in the light unit is not lit. Third data corresponding to difference data between the first data and the second data is generated.

[0018] One embodiment of the present invention is a method for driving an input-output device which includes a first light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a wavelength in a visible light range; a second light unit including a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits provided between the first light unit and the second light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors provided between the first light unit and the second light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal. In the method, in a frame period set by the display selection signal, the first light unit is lit while the Z first light-emitting diodes are sequentially switched and emit light, and the second light unit is lit while the second light-emitting diode emit light. Y pieces of data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second light unit is lit.

[0019] One embodiment of the present invention is a method for driving an input-output device which includes a first light unit including Z (Z is a natural number of 3 or more) first light-emitting diodes that emit light with a

wavelength in a visible light range; a second light unit including a second light-emitting diode that emits light with a wavelength in an infrared range; X (X is a natural number) display circuits provided between the first light unit and the second light unit, supplied with a display selection signal, supplied with a display data signal in accordance with the display selection signal, and set to be in a display state based on data of the input display data signal; and Y (Y is a natural number) photodetectors provided between the first light unit and the second light unit and including a filter for absorbing light with a wavelength in a visible light range, supplied with a photodetection control signal, and generating data based on the illuminance of incident light in accordance with the input photodetection control signal. In the method, in a frame period set by the display selection signal, the first light unit is lit while the Z first light-emitting diodes are sequentially switched and emit light, and the second light unit is lit while the second light-emitting diode emit light. Y pieces of first data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second light unit is lit, and Y pieces of second data based on the illuminance of light incident on the Y photodetectors are generated in a period during which the second light unit is not lit. Third data corresponding to difference data between the first data and the second data is generated.

[0020] According to one embodiment of the present invention, accuracy of photodetection can be improved.

BRIEF DESCRIPTION OF THE DRAWINGS

[0021] In the accompanying drawings:

[0022] FIGS. 1A and 1B illustrate an example of an input-output device in Embodiment 1;

[0023] FIGS. 2A and 2B illustrate an example of an input-output device in Embodiment 2;

[0024] FIGS. 3A and 3B illustrate an example of an input-output device in Embodiment 3;

[0025] FIGS. 4A to 4D illustrate examples of photodetectors in Embodiment 4;

[0026] FIGS. 5A to 5D illustrate examples of display circuits in Embodiment 5;

[0027] FIG. 6 is a schematic cross-sectional view illustrating a structure example of a light unit in Embodiment 6;

[0028] FIGS. 7A to 7D are schematic cross-sectional views each illustrating a structure example of a transistor in Embodiment 7;

[0029] FIGS. 8A to 8E are schematic cross-sectional views illustrating an example of a method for forming the transistor in FIG. 7A;

[0030] FIGS. 9A and 9B illustrate a circuit for evaluating characteristic characteristics;

[0031] FIG. 10A illustrates a relationship between elapsed time Time in measurement of Samples 4, 5, and 6 (SMPs 4, 5, 6) and output voltage V_{out} , and FIG. 10B illustrates a relationship between the elapsed time Time in the measurement of Samples 4, 5, and 6 (SMPs 4, 5, 6) and leakage current calculated from the measurement;

[0032] FIG. 11 illustrates a relationship between voltage of a node A and leakage current estimated from the measurement;

[0033] FIG. 12 illustrates a relationship between voltage of the node A and leakage current estimated from the measurement;

[0034] FIG. 13 illustrates a relationship between voltage of the node A and leakage current estimated from the measurement;

[0035] FIG. 14 illustrates a relationship between voltage of the node A and leakage current estimated from the measurement;

[0036] FIGS. 15A and 15B illustrate a structure example of an active-matrix substrate in Embodiment 8;

[0037] FIGS. 16A and 16B illustrate a structure example of an active-matrix substrate in Embodiment 8;

[0038] FIGS. 17A and 17B illustrate a structure example of an input-output device in Embodiment 8; and

[0039] FIGS. 18A to 18F illustrate structure examples of electronic devices in Embodiment 9.

DETAILED DESCRIPTION OF THE INVENTION

[0040] Examples of embodiments of the present invention will be described below with reference to the drawings. Note that the present invention is not limited to the following description. It will be readily appreciated by those skilled in the art that modes and details of the present invention can be modified in various ways without departing from the spirit and scope of the present invention. The present invention therefore should not be construed as being limited to the following description of the embodiments.

[0041] Note that the contents of the embodiments can be combined with each other as appropriate. In addition, the contents of the embodiments can be replaced with each other.

Embodiment 1

[0042] In this embodiment, an input-output device that can output data and can input data by incident light is described.

[0043] An example of the input-output device in this embodiment is described with reference to FIGS. 1A and 1B. FIGS. 1A and 1B illustrate the example of the input-output device in this embodiment.

[0044] First, a structure example of the input-output device in this embodiment is described with reference to FIG. 1A. FIG. 1A is a schematic diagram illustrating the structure example of the input-output device in this embodiment.

[0045] The input-output device illustrated in FIG. 1A includes a display selection signal output circuit (DSEL-OUT) 101, a display data signal output circuit (DDOUT) 102, a photodetection reset signal output circuit (PR-STOUT) 103a, a photodetection control signal output circuit (PCTLOUT) 103b, an output selection signal output circuit (OSELOUT) 103c, a light unit (LIGHT) 104, X (X is a natural number) display circuits (DISP) 105d, Y (Y is a natural number) photodetectors (PS) 105p, and a reading circuit (READ) 106.

[0046] The display selection signal output circuit 101 has a function of outputting a plurality of display selection signals that are pulse signals (also referred to as signals DSEL).

[0047] The display selection signal output circuit 101 includes, for example, a shift register. The display selection signal output circuit 101 can output display selection signals by output of pulse signals from the shift register.

[0048] A video signal representing an image with an electrical signal is input to the display data signal output

circuit 102. The display data signal output circuit 102 has a function of generating a display data signal (also referred to as a signal DD) that is a voltage signal on the basis of the input video signal and outputting the generated display data signal.

[0049] The display data signal output circuit 102 includes, for example, a transistor.

[0050] Note that in the input-output device, the transistor includes two terminals and a current control terminal for controlling current flowing between the two terminals by applied voltage. Note that without limitation to the transistor, terminals where current flowing therebetween is controlled are also referred to as current terminals. Two current terminals are also referred to as a first current terminal and a second current terminal.

[0051] Further, in the input-output device, a field-effect transistor can be used as the transistor, for example. In a field-effect transistor, a first current terminal, a second current terminal, and a current control terminal are one of a source and a drain, the other of the source and the drain, and a gate, respectively.

[0052] The term “voltage” generally means a difference between potentials at two points (also referred to as a potential difference). However, levels of voltage and potentials are represented by volts (V) in a circuit diagram or the like in some cases, so that it is difficult to distinguish them. Thus, in this specification, a potential difference between a potential at one point and a potential to be a reference (also referred to as a reference potential) is used as voltage at the point in some cases unless otherwise specified.

[0053] The display data signal output circuit 102 can output data of a video signal as a display data signal when the transistor is on. The transistor can be controlled by input of a control signal that is a pulse signal to the current control terminal. Note that in the case where the number of the display circuits 105d is plural, a plurality of transistors may be selectively turned on or off so that data of video signals is output as a plurality of display data signals.

[0054] The photodetection reset signal output circuit 103a has a function of outputting photodetection reset signals that are pulse signals (also referred to as signals PRST).

[0055] The photodetection reset signal output circuit 103a includes, for example, a shift register. The photodetection reset signal output circuit 103a can output photodetection reset signals by output of pulse signals from the shift register.

[0056] The photodetection control signal output circuit 103b has a function of outputting photodetection control signals that are pulse signals (also referred to as signals PCTL). Note that the photodetection control signal output circuit 103b is not necessarily provided.

[0057] The photodetection control signal output circuit 103b includes, for example, a shift register. The photodetection control signal output circuit 103b can output photodetection control signals by output of pulse signals from the shift register.

[0058] The output selection signal output circuit 103c has a function of outputting output selection signals that are pulse signals (also referred to as signals OSEL).

[0059] The output selection signal output circuit 103c includes, for example, a shift register. The output selection signal output circuit 103c can output selection signals by output of pulse signals from the shift register.

[0060] The light unit **104** is a light-emitting unit including a light source.

[0061] The light unit **104** includes Z (Z is a natural number of 3 or more) light-emitting diodes (also referred to as LEDs) **A** and a light-emitting diode **B** as light sources. The lighting state of the light unit **104** varies depending on regions where the different light-emitting diodes are provided.

[0062] The Z light-emitting diodes **A** are light-emitting diodes that emit light with a wavelength in a visible light range (e.g., a wavelength of 360 to 830 nm). For example, a red light-emitting diode, a green light-emitting diode, and a blue light-emitting diode can be used as the Z light-emitting diodes **A**. Note that the number of the light-emitting diodes **A** of each color may be plural. Further, in addition to the red, green, and blue light-emitting diodes, a light-emitting diode of a different color (e.g., a white light-emitting diode) may be used as the Z light-emitting diodes **A**.

[0063] The light-emitting diode **B** is a light-emitting diode that emits light with a wavelength in an infrared range (e.g., a wavelength of greater than 830 nm and less than or equal to 1000 nm).

[0064] Note that, for example, light emission of the light-emitting diode **A** or the light-emitting diode **B** may be controlled with a control signal used for selecting the light-emitting diode **A** or the light emitting diode **B** to which voltage is applied. In addition, a photo regulation circuit for outputting a control signal used for controlling whether the light-emitting diode **A** or the light emitting diode **B** to which voltage is applied is selected may be provided in the light unit **104**.

[0065] Thus, the light unit **104** has a region **A** which is lit by emission of light from the light-emitting diode **A** and a region **B** which is lit by emission of light from the light-emitting diode **B**.

[0066] The display circuit **105d** overlaps with the light unit **104**. To the display circuit **105d**, a display selection signal that is a pulse signal is input, and a display data signal is input in accordance with the input display selection signal. The display circuit **105d** changes its display state in accordance with data of the input display data signal.

[0067] The display circuit **105d** includes, for example, a display selection transistor and a display element.

[0068] The display selection transistor has a function of selecting whether to input data of a display data signal to the display element.

[0069] The display element changes its display state in accordance with data of a display data signal by input of the data of the display data signal by the display selection transistor.

[0070] As the display element, a liquid crystal element or the like can be used, for example.

[0071] As a display mode of the input-output device including a liquid crystal element, a TN (twisted nematic) mode, an IPS (in-plane-switching) mode, an STN (super twisted nematic) mode, a VA (vertical alignment) mode, an ASM (axially symmetric aligned micro-cell) mode, an OCB (optically compensated birefringence) mode, an FLC (ferroelectric liquid crystal) mode, an AFLC (antiferroelectric liquid crystal) mode, an MVA (multi-domain vertical alignment) mode, a PVA (patterned vertical alignment) mode, an ASV (advanced super view) mode, a FFS (fringe field switching) mode, or the like may be used.

[0072] The photodetector **105p** overlaps with the light unit **104**. A photodetection reset signal, a photodetection control signal, and an output selection signal are input to the photodetector **105p**. Note that in the case where the number of the photodetectors **105p** is plural, the same photodetection control signal may be input to the photodetectors **105p**. With such a structure, time required for all the photodetectors to generate optical data can be shortened, and the light incidence time in each photodetector at the time of generating the optical data can be lengthened. Note that a method by which the same photodetection control signal is input to a plurality of photodetectors is also referred to as a global shutter method.

[0073] The photodetector **105p** is set to be in a reset state in accordance with a photodetection reset signal.

[0074] In addition, the photodetector **105p** has a function of generating data that is voltage based on the illuminance of incident light (such data is also referred to as optical data) in accordance with a photodetection control signal.

[0075] Further, the photodetector **105p** has a function of outputting the generated optical data as an optical data signal in accordance with an output selection signal.

[0076] The photodetector **105p** includes, for example, a photoelectric conversion element (PCE), a photodetection reset selection transistor, a photodetection control transistor, an amplifier transistor, and an output selection transistor. The photodetector **105p** further includes a filter for absorbing visible light.

[0077] The photoelectric conversion element is supplied with current (also referred to as photocurrent) in accordance with the illuminance of incident light by incidence of the light on the photoelectric conversion element.

[0078] A photodetection reset signal is input to a current control terminal of the photodetection reset selection transistor. The photodetection reset selection transistor has a function of selecting whether to set the voltage of a current control terminal of the amplifier transistor to reference voltage.

[0079] A photodetection control signal is input to a current control terminal of the photodetection control transistor. The photodetection control transistor has a function of selecting whether to set the voltage of the current control terminal of the amplifier transistor to voltage based on photocurrent flowing to the photoelectric conversion element.

[0080] An output selection signal is input to a current control terminal of the output selection transistor. The output selection transistor has a function of selecting whether to output optical data as an optical data signal from the photodetector **105p**.

[0081] Note that the photodetector **105p** outputs optical data as an optical data signal from a first current terminal or a second current terminal of the amplifier transistor.

[0082] The display circuit **105d** and the photodetector **105p** are provided in a pixel portion **105**. The pixel portion **105** is a region where data is displayed and read. A pixel includes at least one display circuit **105d**. In addition, the pixel may include at least one photodetector **105p**. In the case where the number of the display circuits **105d** is plural, the display circuits **105d** may be arranged in matrix in the pixel portion **105**. Further, in the case where the number of the photodetectors **105p** is plural, the photodetectors **105p** may be arranged in matrix in the pixel portion **105**.

[0083] The reading circuit 106 has a function of selecting the photodetector 105_p for reading optical data and reading the optical data from the selected photodetector 105_p.

[0084] The reading circuit 106 includes, for example, a selector circuit. For example, the selector circuit includes a transistor. The selector circuit can read optical data by input of an optical data signal from the photodetector 105_p with the transistor.

[0085] Next, as an example of a method for driving the input-output device in this embodiment, an example of a method for driving the input-output device illustrated in FIG. 1A is described with reference to FIG. 1B. FIG. 1B is a timing chart for illustrating the example of a method for driving the input-output device illustrated in FIG. 1A.

[0086] In the example of a method for driving the input-output device illustrated in FIG. 1A, in frame periods set in accordance with display selection signals (e.g., frame periods f1 to fn illustrated in FIG. 1B), the Z light-emitting diodes A provided in the light unit 104 are sequentially switched and emit light. Thus, the lighting state of the region A (also referred to as a region 104(VI)) in the light unit 104 is sequentially switched from a lighting state C1 (a state in which the first light-emitting diode A emits light) to a lighting state Ck (a state in which the Z-th light-emitting diode emits light).

[0087] In addition, the light-emitting diode B provided in the light unit 104 emits light, so that the region B (also referred to as a region 104(IR)) in the light unit 104 is set to be in a lighting state LT (a state in which the light-emitting diode B emits light). Note that a period during which the light-emitting diode A emits light may overlap with a period during which the light-emitting diode B emits light.

[0088] In addition, when a display data signal is input to the display circuit 105_d in accordance with the display selection signal and the region A in the light unit 104 is lit, the display circuit 105_d is set to be in a display state based on data of the display data signal. For example, the display state of the display circuit 105_d is a display state dc1 (a display state based on the lighting state C1) when the region A in the light unit 104 is in the lighting state C1; the display state of the display circuit 105_d is a display state dc2 (a display state based on the lighting state C2) when the region A in the light unit 104 is in the lighting state C2; and the display state of the display circuit 105_d is a display state dck (a display state based on the lighting state Ck) when the region A in the light unit 104 is in the lighting state Ck.

[0089] When the light unit 104 in the region B is in the lighting state LT, a pulse (pls) of a photodetection control signal is input to the Y photodetectors 105_p. At this time, the Y photodetectors 105_p generate optical data.

[0090] In addition, the Y photodetectors 105_p output the generated optical data as optical data signals to the reading circuit 106 in accordance with output selection signals so that the optical data is read in the reading circuit 106.

[0091] Note that timing of setting the light unit 104 to be in the lighting state LT may be the same or different in the frame periods.

[0092] As described with reference to FIGS. 1A and 1B, the example of the input-output device in this embodiment includes the display circuit, the plurality of photodetectors including filters for absorbing visible light, and the light unit. The light unit includes a plurality of light-emitting diodes that emit visible light and a light-emitting diode that emits infrared light. With such a structure, the influence of

light in an environment in which the input-output device is placed or infrared light emitted from the light-emitting diode can be reduced when optical data is generated.

[0093] Further, the example of the input-output device in this embodiment has a structure in which part of the light unit is lit while the plurality of light-emitting diodes that emit visible light are sequentially switched and emit light in each frame period. With such a structure, the input-output device can display full-color images.

[0094] Furthermore, the example of the input-output device in this embodiment has a structure in which a region of the light unit in which the light-emitting diode that emits infrared light is provided is lit while the light-emitting diode that emits infrared light emits light in each frame period. With such a structure, the influence of light in the environment in which the input-output device is placed or infrared light emitted from the light-emitting diode can be reduced when optical data is generated. Thus, the light incidence time in each photodetector at the time of generating optical data can be lengthened, so that accuracy of photodetection can be improved.

[0095] Thus, with the structures, accuracy of photodetection can be improved.

Embodiment 2

[0096] In this embodiment, a different example of the input-output device in Embodiment 1 is described. Note that the description in Embodiment 1 is used as appropriate for portions that are the same as those in Embodiment 1.

[0097] An example of the input-output device in this embodiment is described with reference to FIGS. 2A and 2B. FIGS. 2A and 2B illustrate the example of the input-output device in this embodiment.

[0098] First, a structure example of the input-output device in this embodiment is described with reference to FIG. 2A. FIG. 2A is a schematic diagram illustrating the structure example of the input-output device in this embodiment.

[0099] The input-output device illustrated in FIG. 2A includes the display selection signal output circuit 101, the display data signal output circuit 102, the photodetection reset signal output circuit 103_a, the photodetection control signal output circuit 103_b, the output selection signal output circuit 103_c, the light unit 104, the X display circuits 105_d, the Y photodetectors 105_p, the reading circuit 106, and a data processing circuit (DataP) 107.

[0100] Since the display selection signal output circuit 101, the display data signal output circuit 102, the photodetection reset signal output circuit 103_a, the photodetection control signal output circuit 103_b, the output selection signal output circuit 103_c, the light unit 104, the display circuit 105_d, the photodetector 105_p, and the reading circuit 106 are the same as those in the input-output device illustrated in FIG. 1A, the description of each component in the input-output device illustrated in FIG. 1A is used as appropriate.

[0101] The data processing circuit 107 is a circuit which performs arithmetic processing on data of an input data signal. The data processing circuit 107 includes a memory circuit and an arithmetic circuit. The memory circuit has a function of storing data of a data signal. The arithmetic circuit has a function of generating difference data between data of a plurality of data signals by arithmetic processing.

[0102] Note that the data processing circuit 107 may be included in the input-output device. Alternatively, the input-

output device may be electrically connected to a separate data processing means (e.g., a personal computer) having a function equivalent to the function of the data processing circuit. When the data processing circuit 107 is provided in the input-output device, the number of wirings in a portion where the data processing circuit 107 and the reading circuit 106 are connected to each other can be reduced, for example.

[0103] Next, as an example of a method for driving the input-output device in this embodiment, an example of a method for driving the input-output device illustrated in FIG. 2A is described with reference to FIG. 2B. FIG. 2B is a timing chart for illustrating the example of a method for driving the input-output device illustrated in FIG. 2A.

[0104] In the example of a method for driving the input-output device illustrated in FIG. 2A, in frame periods (e.g., the frame periods f1 to fn illustrated in FIG. 2B), the Z light-emitting diodes A provided in the light unit 104 are sequentially switched and emit light. Thus, the lighting state of the region in the light unit 104 where the light-emitting diode A is provided is sequentially switched from the lighting state C1 (the state in which the first light-emitting diode A emits light) to the lighting state Ck (the state in which the Z-th light-emitting diode A emits light). Note that the light unit 104 is not lit between the lighting states.

[0105] In addition, in a certain frame period (the frame period f1 in FIG. 2B), the region in the light unit 104 where the light-emitting diode B is provided is set to be in the lighting state LT while the light-emitting diode B provided in the light unit 104 emits light. Note that a period during which the region in the light unit 104 where the light-emitting diode B is provided is in the lighting state LT may overlap with periods during which the region in the light unit 104 where the light-emitting diode B is provided is in the lighting states C1 to Ck.

[0106] In addition, when a display data signal is input to the display circuit 105d in accordance with the display selection signal and the region in the light unit 104 where the light-emitting diode A is provided is lit, the display circuit 105d is set to be in a display state based on data of the display data signal. For example, the display state of the display circuit 105d is the display state dc1 (the display state based on the lighting state C1) when the region in the light unit 104 where the light-emitting diode A is provided is in the lighting state C1; the display state of the display circuit 105d is the display state dc2 (the display state based on the lighting state C2) when the region in the light unit 104 where the light-emitting diode A is provided is in the lighting state C2; and the display state of the display circuit 105d is the display state dck (the display state based on the lighting state Ck) when the region in the light unit 104 where the light-emitting diode A is provided is in the lighting state Ck.

[0107] When the region in the light unit 104 where the light-emitting diode B is provided is lit, the pulse of a photodetection control signal is input to the Y photodetectors 105p. At this time, the Y photodetectors 105p generate optical data.

[0108] In addition, the Y photodetectors 105p output the generated optical data as optical data signals to the reading circuit 106 in accordance with output selection signals so that the optical data is read in the reading circuit 106. The read optical data is stored in the memory circuit included in the data processing circuit 107.

[0109] In addition, in a frame period that is different from the frame period (the frame period fn in FIG. 2B), when the

region in the light unit 104 where the light-emitting diode B is provided is not lit, the pulse of a photodetection control signal is input to the Y photodetectors 105p. At this time, the Y photodetectors 105p generate optical data.

[0110] In addition, the Y photodetectors 105p output the generated optical data as optical data signals to the reading circuit 106 in accordance with output selection signals so that the optical data is read in the reading circuit 106. The read optical data is stored in the memory circuit included in the data processing circuit 107.

[0111] Further, the arithmetic circuit included in the data processing circuit 107 generates difference data between optical data obtained at the time when the region in the light unit 104 where the light-emitting diode B is provided is in the lighting state LT and optical data obtained at the time when the region in the light unit 104 where the light-emitting diode B is provided is not lit. The difference data is used as data for executing predetermined processing.

[0112] As described with reference to FIGS. 2A and 2B, in the example of the input-output device in this embodiment, optical data at the time when the region in the light unit where the light-emitting diode that emits infrared light is lit and optical data at the time when the region in the light unit where the light-emitting diode that emits infrared light is not lit are generated and difference data between two optical data signals is generated, in addition to the structure described in Embodiment 1. By generation of such difference data, in addition to the advantages described in Embodiment 1, data of light in an environment in which the input-output device is placed can be eliminated from optical data. Thus, the accuracy of photodetection can be further improved.

Embodiment 3

[0113] In this embodiment, a different example of an input-output device that can output data and can input data by incident light is described. Note that the description in Embodiment 1 is used as appropriate for portions that are the same as those in Embodiment 1.

[0114] An example of the input-output device in this embodiment is described with reference to FIGS. 3A and 3B. FIGS. 3A and 3B illustrate the example of the input-output device in this embodiment.

[0115] First, a structure example of the input-output device in this embodiment is described with reference to FIG. 3A. FIG. 3A is a schematic diagram illustrating the structure example of the input-output device in this embodiment.

[0116] The input-output device illustrated in FIG. 3A includes the display selection signal output circuit 101, the display data signal output circuit 102, the photodetection reset signal output circuit 103a, the photodetection control signal output circuit 103b, the output selection signal output circuit 103c, a light unit 104a, a light unit 104b, the X display circuits 105d, the Y photodetectors 105p, and the reading circuit 106.

[0117] Since the display selection signal output circuit 101, the display data signal output circuit 102, the photodetection reset signal output circuit 103a, the photodetection control signal output circuit 103b, the output selection signal output circuit 103c, the display circuit 105d, the photodetector 105p, and the reading circuit 106 are the same as those in the input-output device illustrated in FIG. 1A, the descrip-

tion in each component in the input-output device illustrated in FIG. 1A is used as appropriate.

[0118] The light unit **104a** and the light unit **104b** are light units including light sources.

[0119] The light unit **104a** includes the Z light-emitting diodes A as light sources. The Z light-emitting diodes A are light-emitting diodes that emit visible light. For example, a red light-emitting diode, a green light-emitting diode, and a blue light-emitting diode can be used as the Z light-emitting diodes. Note that the number of the light-emitting diodes of each color may be plural. Further, in addition to the red, green, and blue light-emitting diodes, a light-emitting diode of a different color (e.g., a white light-emitting diode) may be used as the Z light-emitting diodes.

[0120] Note that, for example, light emission of the light-emitting diode A may be controlled with a control signal used for selecting the light-emitting diode A to which voltage is applied. In addition, a photo regulation circuit for outputting a control signal used for controlling whether the light-emitting diode A to which voltage is applied is selected may be provided in the light unit **104a**.

[0121] The light unit **104b** includes the light-emitting diode B as a light source and a light guide plate. The light-emitting diode B is a light-emitting diode that emits infrared light. Note that the number of the light-emitting diodes B may be plural.

[0122] Note that, for example, light emission of the light-emitting diode B may be controlled with a control signal used for selecting the light-emitting diode B to which voltage is applied. In addition, a photo regulation circuit for outputting a control signal used for controlling whether the light-emitting diode B to which voltage is applied is selected may be provided in the light unit **104b**.

[0123] Next, as an example of a method for driving the input-output device in this embodiment, an example of a method for driving the input-output device illustrated in FIG. 3A is described with reference to FIG. 3B. FIG. 3B is a timing chart for illustrating the example of a method for driving the input-output device illustrated in FIG. 3A.

[0124] In the example of a method for driving the input-output device illustrated in FIG. 3A, in frame periods set in accordance with display selection signals (e.g., frame periods f1 to fn illustrated in FIG. 3B), the Z light-emitting diodes A provided in the light unit **104a** are sequentially switched and emit light. Thus, as illustrated in FIG. 3B, the lighting state of the light unit **104a** is sequentially switched from the lighting state C1 (the state in which the first light-emitting diode A emits light) to the lighting state Ck (the state in which the Z-th light-emitting diode emits light).

[0125] When the light-emitting diode B provided in the light unit **104b** emits light, the light unit **104b** is set to be in the lighting state LT, as illustrated in FIG. 3B. Note that periods during which the light unit **104a** is in the lighting state C1 to the lighting state Ck may overlap with a period during which the light unit **104b** is in the lighting state LT.

[0126] In addition, when a display data signal is input to the display circuit **105d** in accordance with the display selection signal and the light unit **104a** is lit, the display circuit **105d** is set to be in a display state based on data of the display data signal. For example, the display state of the display circuit **105d** is the display state dc1 (the display state based on the lighting state C1) when the light unit **104a** is in the lighting state C1; the display state of the display circuit **105d** is the display state dc2 (the display state based

on the lighting state C2) when the light unit **104a** is in the lighting state C2; and the display state of the display circuit **105d** is the display state dck (the display state based on the lighting state Ck) when the light unit **104a** is in the lighting state Ck.

[0127] When the light unit **104b** is lit, a pulse (pls) of a photodetection control signal is input to the Y photodetectors **105p**. At this time, the Y photodetectors **105p** generate optical data.

[0128] In addition, the Y photodetectors **105p** output the generated optical data as optical data signals to the reading circuit **106** in accordance with output selection signals so that the optical data is read in the reading circuit **106**.

[0129] Note that timing of when the light unit **104b** is lit may be the same or different in the frame periods.

[0130] Further, as in the input-output device described in Embodiment 2, optical data at the time when the light unit **104b** is lit and optical data at the time when the light unit **104b** is not lit may be generated and difference data between the two optical data may be generated.

[0131] As described with reference to FIGS. 3A and 3B, the example of the input-output device in this embodiment includes the display circuit, the plurality of photodetectors including filters for absorbing visible light, the first light unit, and the second light unit. The first light unit includes a plurality of light-emitting diodes that emit visible light. The second light unit includes a light-emitting diode that emits infrared light and a light guide plate on which infrared light emitted from the light-emitting diode is incident. With such a structure, light reflected by an object can enter the photodetector only when the object is in contact with the light guide plate provided in the second light unit; thus, accuracy of photodetection can be improved and the influence of light in an environment in which the input-output device is placed or light emitted from the light-emitting diode that emits light with a wavelength in a visible light range can be reduced when optical data is generated.

[0132] Further, the example of the input-output device in this embodiment has a structure in which the region in the light unit where the light-emitting diode that emits visible light is provided is lit while the plurality of light-emitting diodes that emit visible light are sequentially switched and emit light in each frame period. With such a structure, the input-output device can display full-color images.

[0133] Furthermore, the example of the input-output device in this embodiment has a structure in which the second light unit is lit while the light-emitting diode that emits infrared light emits light in each frame period. With such a structure, the influence of light in the environment in which the input-output device is placed or infrared light emitted from the light-emitting diode can be reduced when optical data is generated. Thus, the light incidence time in each photodetector at the time of generating optical data can be lengthened, so that accuracy of photodetection can be improved.

[0134] Thus, with the structures, accuracy of photodetection can be improved.

Embodiment 4

[0135] In this embodiment, examples of the photodetector in the input-output device in the above embodiment are described.

[0136] Examples of the photodetector in this embodiment are described with reference to FIGS. 4A to 4D. FIGS. 4A to 4D illustrate the examples of the photodetector in this embodiment.

[0137] First, structure examples of the photodetector in this embodiment are described with reference to FIGS. 4A and 4B. FIGS. 4A and 4B illustrate the structure examples of the photodetector in this embodiment.

[0138] The photodetector illustrated in FIG. 4A includes a photoelectric conversion element 131a, a transistor 132a, a transistor 133a, and a transistor 134a.

[0139] Note that in the photodetector illustrated in FIG. 4A, the transistor 132a, the transistor 133a, and the transistor 134a are field-effect transistors.

[0140] The photoelectric conversion element 131a has a first current terminal and a second current terminal. A reset signal is input to the first current terminal of the photoelectric conversion element 131a.

[0141] One of a source and a drain of the transistor 134a is electrically connected to the second current terminal of the photoelectric conversion element 131a. A photodetection control signal is input to a gate of the transistor 134a.

[0142] A gate of the transistor 132a is electrically connected to the other of the source and the drain of the transistor 134a.

[0143] One of a source and a drain of the transistor 133a is electrically connected to one of a source and a drain of the transistor 132a. An output selection signal is input to a gate of the transistor 133a.

[0144] Voltage V_a is input to either the other of the source and the drain of the transistor 132a or the other of the source and the drain of the transistor 133a.

[0145] In addition, the photodetector illustrated in FIG. 4A outputs optical data from the rest of the other of the source and the drain of the transistor 132a or the other of the source and the drain of the transistor 133a as an optical data signal.

[0146] The photodetector illustrated in FIG. 4B includes a photoelectric conversion element 131b, a transistor 132b, a transistor 133b, a transistor 134b, and a transistor 135.

[0147] Note that in the photodetector illustrated in FIG. 4B, the transistor 132b, the transistor 133b, the transistor 134b, and the transistor 135 are field-effect transistors.

[0148] The photoelectric conversion element 131b has a first current terminal and a second current terminal. Voltage V_b is input to the first current terminal of the photoelectric conversion element 131b.

[0149] Note that one of the voltage V_a and the voltage V_b is high power supply voltage V_{dd} , and the other of the voltage V_a and the voltage V_b is low power supply voltage V_{ss} . The high supply voltage V_{dd} is voltage whose level is relatively higher than that of the low supply voltage V_{ss} . The low supply voltage V_{ss} is voltage whose level is relatively lower than that of the high supply voltage V_{dd} . The level of the voltage V_a and the level of the voltage V_b might interchange depending, for example, on the polarity of the transistor. A difference between the voltage V_a and the voltage V_b is power supply voltage.

[0150] One of a source and a drain of the transistor 134b is electrically connected to the second current terminal of the photoelectric conversion element 131b. A photodetection control signal is input to a gate of the transistor 134b.

[0151] A gate of the transistor 132b is electrically connected to the other of the source and the drain of the transistor 134b.

[0152] A photodetection reset signal is input to a gate of the transistor 135. The voltage V_a is input to one of a source and a drain of the transistor 135. The other of the source and the drain of the transistor 135 is electrically connected to the other of the source and the drain of the transistor 134b.

[0153] An output selection signal is input to a gate of the transistor 133b. One of a source and a drain of the transistor 133b is electrically connected to one of a source and a drain of the transistor 132b.

[0154] The voltage V_a is input to either the other of the source and the drain of the transistor 132b or the other of the source and the drain of the transistor 133b.

[0155] In addition, the photodetector illustrated in FIG. 4B outputs optical data from the rest of the other of the source and the drain of the transistor 132b or the other of the source and the drain of the transistor 133b as an optical data signal.

[0156] Further, the components of the photodetectors illustrated in FIGS. 4A and 4B are described.

[0157] As the photoelectric conversion elements 131a and 131b, photodiodes, phototransistors, or the like can be used. In the case where the photoelectric conversion elements 131a and 131b are photodiodes, one of an anode and a cathode of the photodiode corresponds to the first current terminal of the photoelectric conversion element, and the other of the anode and the cathode of the photodiode corresponds to the second current terminal of the photoelectric conversion element. In the case where the photoelectric conversion elements 131a and 131b are phototransistors, one of a source and a drain of the phototransistor corresponds to the first current terminal of the photoelectric conversion element, and the other of the source and the drain of the phototransistor corresponds to the second current terminal of the photoelectric conversion element.

[0158] The transistors 132a and 132b function as amplifier transistors.

[0159] The transistors 134a and 134b function as photodetection control transistors. In the photodetector in this embodiment, the transistors 134a and 134b are not necessarily provided. However, with provision of the transistors 134a and 134b, gate voltage of the transistors 132a and 132b can be kept at a desired level for a certain period.

[0160] The transistor 135 functions as a photodetection reset selection transistor.

[0161] The transistors 133a and 133b function as output selection transistors.

[0162] Note that as each of the transistors 132a, 132b, 133a, 133b, 134a, 134b; and 135, for example, it is possible to use a transistor including a semiconductor layer containing a semiconductor that belongs to Group 14 in the periodic table (e.g., silicon) or a transistor including an oxide semiconductor layer. Channels are formed in the semiconductor layer and the oxide semiconductor layer of the transistors. For example, with the use of the transistor including the oxide semiconductor layer, fluctuation in gate voltage due to the leakage current of each of the transistors 132a, 132b, 133a, 133b, 134a, 134b, and 135 can be suppressed.

[0163] Next, examples of methods for driving the photodetectors illustrated in FIGS. 4A and 4B are described.

[0164] First, the example of the method for driving the photodetector illustrated in FIG. 4A is described with reference to FIG. 4C. FIG. 4C is a timing chart for illustrating the example of the method for driving the photodetector illustrated in FIG. 4A, which illustrates states of the photodetection reset signal, the output selection signal, the pho-

photoelectric conversion element **131a**, the transistor **133a**, and the transistor **134a**. Note that the case where the photoelectric conversion element **131a** is a photodiode is described as an example here.

[0165] In the example of the method for driving the photodetector illustrated in FIG. 4A, first, in a period **T31**, the pulse of a photodetection reset signal is input. In the period **T31** and a period **T32**, the pulse of a photodetection control signal is input. Note that in the period **T31**, timing of starting input of the pulse of the photodetection reset signal may be earlier than timing of starting input of the pulse of the photodetection control signal.

[0166] In that case, in the period **T31**, the photoelectric conversion element **131a** is in a state in which current flows in a forward direction (also referred to as a state **ST51**), the transistor **134a** is turned on, and the transistor **133a** is turned off.

[0167] At this time, the voltage of the gate of the transistor **132a** is reset to a certain level.

[0168] Then, in the period **T32** after the input of the pulse of the photodetection reset signal, the photoelectric conversion element **131a** is set to be in a state in which voltage is applied in a reverse direction (also referred to as a state **ST52**), and the transistor **133a** is kept off.

[0169] At this time, photocurrent flows between the first current terminal and the second current terminal of the photoelectric conversion element **131a** in accordance with the illuminance of light incident on the photoelectric conversion element **131a**. Further, the voltage level of the gate of the transistor **132a** is changed in accordance with the photocurrent. In that case, channel resistance between the source and the drain of the transistor **132a** is changed.

[0170] Further, in a period **T33** after the input of the pulse of the photodetection control signal, the transistor **134a** is turned off.

[0171] At this time, the voltage of the gate of the transistor **132a** is kept to be a level corresponding to the photocurrent of the photoelectric conversion element **131a** in the period **T32**. Note that the period **T33** is not necessarily provided; however, with provision of the period **T33**, timing of outputting an optical data signal in the photodetector can be set as appropriate. For example, timing of outputting an optical data signal in each of the plurality of photodetectors can be set as appropriate.

[0172] Then, in a period **T34**, the pulse of the output selection signal is input.

[0173] At this time, the photoelectric conversion element **131a** is kept in the state **ST52**, the transistor **133a** is turned on, and current flows through the source and the drain of the transistor **132a** and the source and the drain of the transistor **133a**. The amount of the current flowing through the source and the drain of the transistor **132a** and the source and the drain of the transistor **133a** depends on the voltage level of the gate of the transistor **132a**. Thus, optical data has a value based on the illuminance of light incident on the photoelectric conversion element **131a**. In addition, the photodetector illustrated in FIG. 4A outputs optical data from the rest of the other of the source and the drain of the transistor **132a** or the other of the source and the drain of the transistor **133a** as an optical data signal. That is the example of the method for driving the photodetector illustrated in FIG. 4A.

[0174] Next, the example of the method for driving the photodetector illustrated in FIG. 4B is described with ref-

erence to FIG. 4D. FIG. 4D is a timing chart for illustrating the example of the method for driving the photodetector illustrated in FIG. 4B.

[0175] In the example of the method for driving the photodetector illustrated in FIG. 4B, first, in a period **T41**, the pulse of a photodetection reset signal is input. In the period **T41** and a period **T42**, the pulse of a photodetection control signal is input. Note that in the period **T41**, timing of starting input of the pulse of the photodetection reset signal may be earlier than timing of starting input of the pulse of the photodetection control signal.

[0176] At this time, in the period **T41**, the photoelectric conversion element **131b** is set to be in the state **ST51**, and the transistor **134b** is turned on, so that the voltage level of the gate of the transistor **132b** is reset to a level equivalent to the level of the voltage V_a .

[0177] Further, in the period **T42** after the input of the pulse of the photodetection reset signal, the photoelectric conversion element **131b** is set to be in the state **ST52**, the transistor **134b** is kept on, and the transistor **135** is turned off.

[0178] At this time, photocurrent flows between the first current terminal and the second current terminal of the photoelectric conversion element **131b** in accordance with the illuminance of light incident on the photoelectric conversion element **131b**. Further, the voltage level of the gate of the transistor **132b** is changed in accordance with the photocurrent. In that case, channel resistance between the source and the drain of the transistor **132b** is changed.

[0179] Further, in a period **T43** after the input of the pulse of the photodetection control signal, the transistor **134b** is turned off.

[0180] At this time, the voltage of the gate of the transistor **132b** is kept to be a level corresponding to the photocurrent of the photoelectric conversion element **131b** in the period **T42**. Note that the period **T43** is not necessarily provided; however, with provision of the period **T43**, timing of outputting an optical data signal in the photodetector can be set as appropriate. For example, timing of outputting an optical data signal in each of the plurality of photodetectors can be set as appropriate.

[0181] In a period **T44**, the pulse of the output selection signal is input.

[0182] At this time, the photoelectric conversion element **131b** is kept in the state **ST52** and the transistor **133b** is turned on.

[0183] When the transistor **133b** is turned on, the photodetector illustrated in FIG. 4B outputs an optical data signal from the rest of the other of the source and the drain of the transistor **132b** or the other of the source and the drain of the transistor **133b**. The amount of current flowing through the source and the drain of the transistor **132b** and the source and the drain of the transistor **133b** depends on the voltage level of the gate of the transistor **132b**. Thus, optical data has a value based on the illuminance of light incident on the photoelectric conversion element **131b**. That is the example of the method for driving the photodetector illustrated in FIG. 4B.

[0184] As described with reference to FIGS. 4A to 4D, the example of the photodetector in this embodiment includes the photoelectric conversion element, the photodetection control transistor, and the amplifier transistor. The example of the photodetector in this embodiment has a structure in which optical data is generated in accordance with a pho-

photodetection control signal and is output as a data signal in accordance with an output selection signal. With such a structure, the photodetector can generate and output optical data.

Embodiment 5

[0185] In this embodiment, examples of the display circuit in the input-output device in the above embodiment are described.

[0186] Examples of the display circuit in this embodiment are described with reference to FIGS. 5A to 5D. FIGS. 5A to 5D illustrate the examples of the display circuit in this embodiment.

[0187] First, structure examples of the display circuit in this embodiment are described with reference to FIGS. 5A and 5B. FIGS. 5A and 5B illustrate the structure examples of the display circuit in this embodiment.

[0188] The display circuit illustrated in FIG. 5A includes a transistor 151a, a liquid crystal element 152a, and a capacitor 153a.

[0189] Note that in the display circuit illustrated in FIG. 5A, the transistor 151a is a field-effect transistor.

[0190] In addition, in the input-output device, the liquid crystal element includes a first display electrode, a second display electrode, and a liquid crystal layer. The light transmittance of the liquid crystal layer changes depending on voltage applied between the first display electrode and the second display electrode.

[0191] Further, in the input-output device, the capacitor includes a first capacitor electrode, a second capacitor electrode, and a dielectric layer overlapping with the first capacitor electrode and the second capacitor electrode. Electrical charge is accumulated in the capacitor in accordance with voltage applied between the first capacitor electrode and the second capacitor electrode.

[0192] A display data signal is input to one of a source and a drain of the transistor 151a, and a display selection signal is input to a gate of the transistor 151a.

[0193] The first display electrode of the liquid crystal element 152a is electrically connected to the other of the source and the drain of the transistor 151a. Voltage V_c is input to the second display electrode of the liquid crystal element 152a. The level of the voltage V_c can be set as appropriate.

[0194] The first capacitor electrode of the capacitor 153a is electrically connected to the other of the source and the drain of the transistor 151a. The voltage V_c is input to the second capacitor electrode of the capacitor 153a.

[0195] The display circuit illustrated in FIG. 5B includes a transistor 151b, a liquid crystal element 152b, a capacitor 153b, a capacitor 154, a transistor 155, and a transistor 156.

[0196] Note that in the display circuit illustrated in FIG. 5B, the transistor 151b, the transistor 155, and the transistor 156 are field-effect transistors.

[0197] A display data signal is input to one of a source and a drain of the transistor 155. A write selection signal (also referred to as a signal WSEL) that is a pulse signal is input to a gate of the transistor 155. The write selection signal can be generated by output of a pulse signal from a shift register included in a circuit, for example.

[0198] A first capacitor electrode of the capacitor 154 is electrically connected to the other of the source and the drain of the transistor 155. The voltage V is input to a second capacitor electrode of the capacitor 154.

[0199] One of a source and a drain of the transistor 151b is electrically connected to the other of the source and the drain of the transistor 155. A display selection signal is input to a gate of the transistor 151b.

[0200] A first display electrode of the liquid crystal element 152b is electrically connected to the other of the source and the drain of the transistor 151b. The voltage V_c is input to a second display electrode of the liquid crystal element 152b.

[0201] A first capacitor electrode of the capacitor 153b is electrically connected to the other of the source and the drain of the transistor 151b. The voltage V_c is input to a second capacitor electrode of the capacitor 153b. The level of the voltage V_c is set as appropriate in accordance with the specification of the display circuit.

[0202] Reference voltage is input to one of a source and a drain of the transistor 156. The other of the source and the drain of the transistor 156 is electrically connected to the other of the source and the drain of the transistor 151b. A display reset signal (also referred to as a signal DRST) that is a pulse signal is input to a gate of the transistor 156.

[0203] Further, the components of the display circuits illustrated in FIGS. 5A and 5B are described.

[0204] The transistors 151a and 151b function as display selection transistors.

[0205] As each of the liquid crystal layers of the liquid crystal elements 152a and 152b, a liquid crystal layer for transmitting light when voltage applied to a first display electrode and a second display electrode is 0 V can be used. For example, a liquid crystal layer containing an electrically controlled birefringence liquid crystal (also referred to as an ECB liquid crystal), a liquid crystal to which a dichroic pigment is added (also referred to as a GH liquid crystal), a polymer dispersed liquid crystal, or a discotic liquid crystal can be used. A liquid crystal layer exhibiting a blue phase may be used as the liquid crystal layer. The liquid crystal layer exhibiting a blue phase contains, for example, a liquid crystal composition including a liquid crystal exhibiting a blue phase and a chiral agent. The liquid crystal exhibiting a blue phase has a short response time of 1 ms or less, and is optically isotropic; thus, alignment treatment is not needed and viewing angle dependence is small. Thus, with the liquid crystal exhibiting a blue phase, operation speed can be improved. For example, the filed-sequential input-output device in the above embodiment needs higher operation speed than a display device using a color filter; thus, it is preferable that the liquid crystal exhibiting a blue phase be used in the liquid crystal element in the filed-sequential input-output device in the above embodiment.

[0206] The capacitor 153a functions as a storage capacitor in which voltage whose level is based on a display data signal is applied between the first capacitor electrode and the second capacitor electrode with the transistor 151a. The capacitor 153b functions as a storage capacitor in which voltage whose level is based on a display data signal is applied between the first capacitor electrode and the second capacitor electrode with the transistor 151b. The capacitors 153a and 153b are not necessarily provided; however, with the capacitors 153a and 153b, fluctuation in voltage applied to the liquid crystal elements due to the leakage current of the display selection transistors can be suppressed.

[0207] The capacitor 154 functions as a storage capacitor in which voltage whose level is based on a display data

signal is applied between the first capacitor electrode and the second capacitor electrode with the transistor **155**.

[0208] The transistor **155** functions as a write selection transistor for selecting whether a display data signal is input to the capacitor **154**.

[0209] The transistor **156** functions as a display reset selection transistor for selecting whether voltage applied to the liquid crystal element **152b** is reset.

[0210] Note that as each of the transistors **151a**, **151b**, **155**, and **156**, for example, it is possible to use a transistor including a semiconductor layer containing a semiconductor that belongs to Group 14 in the periodic table (e.g., silicon) or a transistor including an oxide semiconductor layer. Channels are formed in the semiconductor layer and the oxide semiconductor layer of the transistors.

[0211] Next, examples of methods for driving the display circuits illustrated in FIGS. **5A** and **5B** are described.

[0212] First, the example of the method for driving the display circuit illustrated in FIG. **5A** is described with reference to FIG. **5C**. FIG. **5C** is a timing chart for describing the example of the method for driving the display circuit illustrated in FIG. **5A**, which illustrates states of the display data signal and the display selection signal.

[0213] In the example of the method for driving the display circuit illustrated in FIG. **5A**, the transistor **151a** is turned on by input of the pulse of the display selection signal.

[0214] When the transistor **151a** is turned on, a display data signal is input to the display circuit, so that the voltage level of the first display electrode of the liquid crystal element **152a** and the voltage level of the first capacitor electrode of the capacitor **153a** are equivalent to the voltage level of the display data signal.

[0215] At this time, the liquid crystal element **152a** is set to be in a write state (also referred to as a state wt) and the light transmittance of the liquid crystal element **152a** is based on the display data signal, so that the display circuit is set to be in a display state based on data of the display data signal (data **D11** to data **DX**).

[0216] Then, the transistor **151a** is turned off, and the liquid crystal element **152a** is set to be in a hold state (also referred to as a state hld) and holds voltage applied between the first display electrode and the second display electrode so that the amount of fluctuation in the voltage from the initial value does not exceed a reference value until when the next pulse of the display selection signal is input. In addition, when the liquid crystal element **152a** is in the hold state, the light unit in the input-output device in the above embodiment is lit.

[0217] Next, the example of the method for driving the display circuit illustrated in FIG. **5B** is described with reference to FIG. **5D**. FIG. **5D** is a timing chart for illustrating the example of the method for driving the display circuit illustrated in FIG. **5B**.

[0218] In the example of the method for driving the display circuit illustrated in FIG. **5B**, the transistor **156** is turned on by input of the pulse of the display reset signal, so that the voltage of the first display electrode of the liquid crystal element **152b** and the voltage of the first capacitor electrode of the capacitor **153b** are reset to the reference voltage.

[0219] The transistor **155** is turned on by input of the pulse of a write selection signal, and a display data signal is input to the display circuit, so that the voltage level of the first

capacitor electrode of the capacitor **154** is equivalent to the voltage level of the display data signal.

[0220] After that, the transistor **151b** is turned on by input of the pulse of the display selection signal, so that the voltage level of the first display electrode of the liquid crystal element **152b** and the voltage level of the first capacitor electrode of the capacitor **153b** are equivalent to the voltage level of the first capacitor electrode of the capacitor **154**.

[0221] At this time, the liquid crystal element **152b** is set to be in a write state and the light transmittance of the liquid crystal element **152b** is based on the display data signal, so that the display circuit is set to be in a display state based on data of the display data signal (data **D11** to data **DX**).

[0222] Then, the transistor **151b** is turned off, and the liquid crystal element **152b** is set to be in a hold state and holds voltage applied between the first display electrode and the second display electrode so that the amount of fluctuation in the voltage from the initial value does not exceed a reference value until when the next pulse of the display selection signal is input. In addition, when the liquid crystal element **152b** is in the hold state, the light unit in the input-output device in the above embodiment is lit.

[0223] As described with reference to FIGS. **5A** and **5B**, the example of the display circuit in this embodiment has a structure in which the display selection transistor and the liquid crystal element are provided. With such a structure, the display circuit can be set to be in a display state based on a display data signal.

[0224] Further, as described with reference to FIG. **5B**, the example of the display circuit in this embodiment has a structure in which the write selection transistor and the capacitor are provided in addition to the display selection transistor and the liquid crystal element. With such a structure, while the liquid crystal element is set to be in a display state based on data of a display data signal, data of the next display data signal can be written to the capacitor. Thus, the operation speed of the display circuit can be improved.

Embodiment 6

[0225] In this embodiment, an example of the second light unit of the input-output device in Embodiment 2 is described.

[0226] A structure example of a light unit in this embodiment is described with reference to FIG. **6**. FIG. **6** is a schematic view illustrating the structure example of the light unit in this embodiment.

[0227] The light unit illustrated in FIG. **6** includes a light source **201**, a light guide plate **202**, and a fixing member **203**. Further, the light unit illustrated in FIG. **6** overlaps with a photodetector in a pixel portion (PX) **205**.

[0228] As the light source **201**, a light-emitting diode that emits light with a wavelength in an infrared range can be used, as described in Embodiment 2.

[0229] The fixing member **203** has a function of fixing the light source **201** and the light guide plate **202**. A light-blocking material is preferably used for the fixing member **203**. With the use of a light-blocking material for the fixing member **203**, leakage of light emitted from the light source **201** to the outside can be prevented. Note that the fixing member **203** is not necessarily provided.

[0230] In the light unit illustrated in FIG. **6**, light emitted from the light source **201** enters the light guide plate **202**. For example, in the case where an object is not in contact

with the light guide plate 202, light emitted from the light source 201 is totally reflected in the light guide plate 202. Further, in the case where an object (e.g., a finger 204) is in contact with the light guide plate 202, light emitted from the light source 201 is scattered in a portion where the finger 204 is in contact with the light guide plate 202 and enters the photodetector.

[0231] On and off of the light unit illustrated in FIG. 6 may be switched by a photo regulation circuit.

[0232] As described with reference to FIG. 6, in the example of the light unit in this embodiment, the light source and the light guide plate are provided, light emitted from the light source is totally reflected in the light guide plate, and when the object is in contact with the light guide plate, in the contact portion, light reflected by the object enter the photodetector. With such a structure, the influence of light in an environment in which the input-output device is placed can be reduced.

Embodiment 7

[0233] In this embodiment, transistors that can be used as transistors included in the input-output device described in the above embodiment are described.

[0234] In the input-output device described in the above embodiment, as the transistor, for example, it is possible to use a transistor including a semiconductor layer containing a semiconductor that belongs to Group 14 in the periodic table (e.g., silicon) or a transistor including an oxide semiconductor layer. Channels are formed in the semiconductor layer and the oxide semiconductor layer of the transistors. Note that a layer in which a channel is formed is also referred to as a channel formation layer.

[0235] Note that the semiconductor layer may be a single crystal semiconductor layer, a polycrystalline semiconductor layer, a microcrystalline semiconductor layer, or an amorphous semiconductor layer.

[0236] In the input-output device described in the above embodiment, as the transistor including the oxide semiconductor layer, for example, a transistor including an oxide semiconductor layer that is highly purified to be intrinsic (also referred to as i-type) or substantially intrinsic can be used. Purification is a general idea including the following cases: the case where hydrogen in an oxide semiconductor layer is removed as much as possible and the case where oxygen is supplied to an oxide semiconductor layer and defects due to oxygen deficiency of the oxide semiconductor layer are reduced.

[0237] Structure examples of the transistor including the oxide semiconductor layer are described with reference to FIGS. 7A to 7D. FIGS. 7A to 7D are schematic cross-sectional views each illustrating a structure example of the transistor in this embodiment.

[0238] The transistor illustrated in FIG. 7A is a kind of bottom-gate transistor called an inverted-staggered transistor.

[0239] The transistor illustrated in FIG. 7A includes a conductive layer 401a, an insulating layer 402a, an oxide semiconductor layer 403a, a conductive layer 405a, and a conductive layer 406a.

[0240] The conductive layer 401a is provided over a substrate 400a. The insulating layer 402a is provided over the conductive layer 401a. The oxide semiconductor layer 403a overlaps with the conductive layer 401a with the insulating layer 402a provided therebetween. The conduc-

tive layer 405a and the conductive layer 406a are each provided over part of the oxide semiconductor layer 403a.

[0241] Further, in the transistor illustrated in FIG. 7A, part of a top surface of the oxide semiconductor layer 403a (part of the oxide semiconductor layer 403a over which neither the conductive layer 405a nor the conductive layer 406a is provided) is in contact with an oxide insulating layer 407a.

[0242] A transistor illustrated in FIG. 7B is a kind of bottom-gate transistor called a channel-protective (channel-stop) transistor and is also called an inverted-staggered transistor.

[0243] The transistor illustrated in FIG. 5B includes a conductive layer 401b, an insulating layer 402b, an oxide semiconductor layer 403b, a conductive layer 405b, a conductive layer 406b, and an oxide insulating layer 407b.

[0244] The conductive layer 401b is provided over a substrate 400b. The insulating layer 402b is provided over the conductive layer 401b. The oxide semiconductor layer 403b overlaps with the conductive layer 401b with the insulating layer 402b provided therebetween. The oxide insulating layer 407b is provided over the oxide semiconductor layer 403b. The conductive layer 405b and the conductive layer 406b are provided over part of the oxide semiconductor layer 403b with the oxide insulating layer 407b provided therebetween.

[0245] A transistor illustrated in FIG. 7C is a kind of bottom-gate transistor.

[0246] The transistor illustrated in FIG. 7C includes a conductive layer 401c, an insulating layer 402c, an oxide semiconductor layer 403c, a conductive layer 405c, and a conductive layer 406c.

[0247] The conductive layer 401c is provided over a substrate 400c. The insulating layer 402c is provided over the conductive layer 401c. The conductive layer 405c and the conductive layer 406c are provided over part of the insulating layer 402c. The oxide semiconductor layer 403c overlaps with the conductive layer 401c with the insulating layer 402c provided therebetween.

[0248] Further, in FIG. 7C, an upper surface and side surfaces of the oxide semiconductor layer 403c in the transistor are in contact with an oxide insulating layer 407c.

[0249] Note that in FIGS. 7A to 7C, a protective insulating layer may be provided over the oxide insulating layer.

[0250] A transistor illustrated in FIG. 7D is a kind of top-gate transistor.

[0251] The transistor illustrated in FIG. 7D includes a conductive layer 401d, an insulating layer 402d, an oxide semiconductor layer 403d, a conductive layer 405d, and a conductive layer 406d.

[0252] The oxide semiconductor layer 403d is provided over a substrate 400d with an insulating layer 447 provided therebetween. The conductive layer 405d and the conductive layer 406d are provided over part of the oxide semiconductor layer 403d. The insulating layer 402d is provided over the oxide semiconductor layer 403d, the conductive layer 405d, and the conductive layer 406d. The conductive layer 401d overlaps with the oxide semiconductor layer 403d with the insulating layer 402d provided therebetween.

[0253] Further, components illustrated in FIGS. 7A to 7D are described.

[0254] As each of the substrates 400a to 400d, a light-transmitting substrate such as a glass substrate or a plastic substrate can be used, for example.

[0255] The insulating layer 447 functions as a base layer for preventing diffusion of impurity elements from the substrate 400d.

[0256] The insulating layer 447 can be, for example, a silicon nitride layer, a silicon oxide layer, a silicon nitride oxide layer, a silicon oxynitride layer, an aluminum oxide layer, or an aluminum oxynitride layer. The insulating layer 447 can be formed using a stack of materials which can be used for the insulating layer 447.

[0257] The conductive layers 401a to 401d each function as a gate of the transistor. Note that a layer functioning as a gate of a transistor is also referred to as a gate electrode or a gate wiring.

[0258] Note that the transistor in this embodiment may include a conductive layer overlapping with the conductive layer functioning as a gate with the oxide semiconductor layer provided therebetween, in addition to the components of the transistors illustrated in FIGS. 7A to 7D. The conductive layer also functions as a gate of the transistor. With such a structure, the threshold voltage of the transistor can be controlled and light can be prevented from entering the oxide semiconductor layer.

[0259] Each of the conductive layers 401a to 401d can be, for example, a layer of a metal material such as molybdenum, titanium, chromium, tantalum, tungsten, aluminum, copper, neodymium, or scandium or an alloy material containing the metal material as a main component. The conductive layers 401a to 401d may be formed using a stack of materials which can be used for the conductive layers 401a to 401d.

[0260] The insulating layers 402a to 402d each function as a gate insulating layer of the transistor. Note that a layer functioning as a gate insulating layer of a transistor is also referred to as a gate insulating layer.

[0261] As each of the insulating layers 402a to 402c, a silicon oxide layer, a silicon nitride layer, a silicon oxynitride layer, a silicon nitride oxide layer, an aluminum oxide layer, an aluminum nitride layer, an aluminum oxynitride layer, an aluminum nitride oxide layer, or a hafnium oxide layer can be used, for example. The insulating layers 402a to 402c can be formed using a stack of materials which can be used for the insulating layers 402a to 402c. The oxide insulating layer 402d can be an oxide insulating layer, for example, a silicon oxide layer.

[0262] The oxide semiconductor layers 403a to 403d each function as a layer in which a channel of the transistor is formed. Examples of an oxide semiconductor that can be used for the oxide semiconductor layers 403a to 403d include a four-component metal oxide, a three-component metal oxide, and a two-component metal oxide. The oxide semiconductor includes at least one element selected from In, Ga, Sn, Zn, Al, Mg, Hf, or lanthanoid. As the four-component metal oxide, an In—Sn—Ga—Zn—O-based metal oxide or the like can be used, for example. As the three-component metal oxide, an In—Ga—Zn—O-based metal oxide, an In—Sn—Zn—O-based metal oxide, an In—Al—Zn—O-based metal oxide, a Sn—Ga—Zn—O-based metal oxide, an Al—Ga—Zn—O-based metal oxide, a Sn—Al—Zn—O-based metal oxide, an In—Hf—Zn—O-based metal oxide, an In—La—Zn—O-based metal oxide, an In—Ce—Zn—O-based metal oxide, an In—Pr—Zn—O-based metal oxide, an In—Nd—Zn—O-based metal oxide, an In—Pm—Zn—O-based metal oxide, an In—Sm—Zn—O-based metal oxide, an In—Eu—Zn—O-based metal

oxide, an In—Gd—Zn—O-based metal oxide, an In—Tb—Zn—O-based metal oxide, an In—Dy—Zn—O-based metal oxide, an In—Ho—Zn—O-based metal oxide, an In—Er—Zn—O-based metal oxide, an In—Tm—Zn—O-based metal oxide, an In—Yb—Zn—O-based metal oxide, an In—Lu—Zn—O-based metal oxide, or the like can be used, for example. As the two-component metal oxide, an In—Zn—O-based metal oxide, a Sn—Zn—O-based metal oxide, an Al—Zn—O-based metal oxide, a Zn—Mg—O-based metal oxide, a Sn—Mg—O-based metal oxide, an In—Mg—O-based metal oxide, an In—Sn—O-based metal oxide, an In—Ga—O-based metal oxide, or the like can be used, for example. An In—O-based metal oxide, a Sn—O-based metal oxide, a Zn—O-based metal oxide, or the like can be used as the oxide semiconductor, for example. The metal oxide that can be used as the oxide semiconductor may contain silicon oxide.

[0263] In the case where an In—Zn—O-based metal oxide is used, for example, an oxide target having the following composition ratios can be used for deposition of an In—Zn—O-based metal oxide semiconductor layer: In:Zn=50:1 to 1:2 (In₂O₃:ZnO=25:1 to 1:4 in a molar ratio), preferably In:Zn=20:1 to 1:1 (In₂O₃:ZnO=10:1 to 1:2 in a molar ratio), more preferably In:Zn=15:1 to 1.5:1 (In₂O₃:ZnO=15:2 to 3:4 in a molar ratio). For example, when the atomic ratio of the target used for the deposition of the In—Zn—O-based oxide semiconductor is expressed by In:Zn:O=P:Q:R, R>1. 5P+Q. The increase in the In content makes the mobility of the transistor higher.

[0264] As the oxide semiconductor, a material represented by InMO₃(ZnO)_m (m is larger than 0) can be used. Here, M in InMO₃(ZnO)_m represents one or more metal elements selected from Ga, Al, Mn, or Co.

[0265] The conductive layers 405a to 405d and the conductive layers 406a to 406d each function as a source or a drain of the transistor. Note that a layer functioning as a source of a transistor is also referred to as a source electrode or a source wiring, and a layer functioning as a drain of a transistor is also referred to as a drain electrode or a drain wiring.

[0266] Each of the conductive layers 405a to 405d and the conductive layers 406a to 406d can be, for example, a layer of a metal material such as aluminum, chromium, copper, tantalum, titanium, molybdenum, or tungsten; or an alloy material containing the metal material as a main component. The conductive layers 405a to 405d and the conductive layers 406a to 406d can be formed using a stack of materials which can be used for the conductive layers 405a to 405d and the conductive layers 406a to 406d.

[0267] Alternatively, each of the conductive layers 405a to 405d and the conductive layers 406a to 406d can be a layer containing a conductive metal oxide. As the conductive metal oxide, indium oxide, tin oxide, zinc oxide, an alloy of indium oxide and tin oxide, or an alloy of indium oxide and zinc oxide can be used, for example. Note that the conductive metal oxide which can be used for each of the conductive layers 405a to 405d and the conductive layers 406a to 406d may contain silicon oxide.

[0268] The oxide insulating layers 407a to 407c can be, for example, a silicon oxide layer or the like. Note that the oxide insulating layer 407b functions as a layer for protecting a channel formation layer of the transistor (such a layer is also referred to as a channel protective layer).

[0269] Note that the transistor in this embodiment does not necessarily have a structure in which the entire oxide semiconductor layer overlaps with the conductive layer functioning as a gate electrode as illustrated in FIGS. 7A to 7D. However, when the transistor in this embodiment has a structure in which the entire oxide semiconductor layer overlaps with the conductive layer functioning as a gate electrode, light can be prevented from entering the oxide semiconductor layer.

[0270] As an example of a method for forming the transistor in this embodiment, an example of a method for forming the transistor illustrated in FIG. 7A is described with reference to FIGS. 8A to 8E. FIGS. 8A to 8E are schematic cross-sectional views illustrating the example of the method for forming the transistor in FIG. 7A.

[0271] First, as illustrated in FIG. 8A, the substrate 400a is prepared and a first conductive film is formed over the substrate 400a. Part of the first conductive film is etched so that the conductive layer 401a is formed.

[0272] For example, the first conductive film can be formed by formation of a layer of a material that can be used for the conductive layer 401a by sputtering. Alternatively, the first conductive film can be formed using a stack of layers of materials that can be used for the conductive layer 401a.

[0273] Note that when a high-purity gas from which an impurity such as hydrogen, water, a hydroxyl group, or hydride is removed is used as a sputtering gas, for example, the impurity concentration in the film can be lowered.

[0274] Note that preheating treatment may be performed in a preheating chamber of a sputtering apparatus before the film is formed by sputtering. By the preheating treatment, an impurity such as hydrogen or moisture can be eliminated.

[0275] Before the film is formed by sputtering, for example, treatment by which voltage is applied to a target side, not to a target side, in an argon, nitrogen, helium, or oxygen atmosphere with the use of an RF power and plasma is generated so that a surface of the substrate on which the film is formed is modified (such treatment is also referred to as reverse sputtering) may be performed. By reverse sputtering, powdery substances (also referred to as particles or dust) that attach onto the surface on which the film is formed can be removed.

[0276] In the case where the film is formed by sputtering, moisture remaining in a deposition chamber for the film can be removed by an adsorption vacuum pump or the like. A cryopump, an ion pump, a titanium sublimation pump, or the like can be used as the adsorption vacuum pump. Alternatively, moisture remaining in the deposition chamber can be removed by a turbo pump provided with a cold trap.

[0277] For example, a resist mask is formed over part of the first conductive film by a photolithography process and the first conductive film is etched using the resist mask, so that the conductive layer 401a can be formed. Note that in that case, the resist mask is removed after the conductive layer 401a is formed.

[0278] The resist mask may be formed by an inkjet method. A photomask is not needed in an inkjet method; thus, manufacturing cost can be reduced. In addition, the resist mask may be formed using an exposure mask having a plurality of regions with different transmittances (such an exposure mask is also referred to as a multi-tone mask). With the multi-tone mask, a resist mask having a plurality of

regions with different thicknesses can be formed, so that the number of resist masks used for the formation of the transistor can be reduced.

[0279] Next, as illustrated in FIG. 8B, the insulating layer 402a is formed by formation of a first insulating film over the conductive layer 401a.

[0280] For example, the first insulating film can be formed by formation of a layer of a material that can be used for the insulating layer 402a by sputtering, plasma-enhanced CVD, or the like. The first insulating film can be formed by a stack of layers of materials that can be used for the insulating layer 402a. Further, when the layer of a material that can be used for the insulating layer 402a is formed by high-density plasma-enhanced CVD (e.g., high-density plasma-enhanced CVD using microwaves (e.g., microwaves with a frequency of 2.45 GHz)), the insulating layer 402a can be dense and can have higher breakdown voltage.

[0281] Then, as illustrated in FIG. 8C, an oxide semiconductor film is formed over the insulating layer 402a. After that, part of the oxide semiconductor film is etched so that the oxide semiconductor layer 403a is formed.

[0282] For example, the oxide semiconductor film can be formed by formation of a layer of an oxide semiconductor material that can be used for the oxide semiconductor layer 403a by sputtering. Note that the oxide semiconductor film may be formed in a rare gas atmosphere, an oxygen atmosphere, or a mixed atmosphere of a rare gas and oxygen.

[0283] For example, the oxide semiconductor film can be formed using an oxide target having a composition ratio of $\text{In}_2\text{O}_3:\text{Ga}_2\text{O}_3:\text{ZnO}=1:1:1$ (in a molar ratio) as a sputtering target. Alternatively, for example, the oxide semiconductor film may be formed using an oxide target having a composition ratio of $\text{In}_2\text{O}_3:\text{Ga}_2\text{O}_3:\text{ZnO}=1:1:2$ (in a molar ratio).

[0284] When the oxide semiconductor film is formed by sputtering, the substrate 400a may be kept under reduced pressure and heated at 100 to 600° C., preferably 200 to 400° C. By heating of the substrate 400a, the impurity concentration in the oxide semiconductor film can be lowered and damage to the oxide semiconductor film during the sputtering can be reduced.

[0285] For example, the oxide semiconductor film can be etched using a resist mask which is formed over part of the oxide semiconductor film by a photolithography process, so that the oxide semiconductor layer 403a can be formed. Note that in that case, the resist mask is removed after the oxide semiconductor film is etched.

[0286] Then, as illustrated in FIG. 8D, a second conductive film is formed over the insulating layer 402a and the oxide semiconductor layer 403a and partly etched so that the conductive layers 405a and 406a are formed.

[0287] For example, the second conductive film can be formed by formation of a layer of a material that can be used for the conductive layers 405a and 406a by sputtering or the like. Alternatively, the second conductive film can be formed using a stack of films of materials that can be used for the conductive layers 405a and 406a.

[0288] For example, a resist mask is formed over part of the second conductive film by a photolithography process and the second conductive film is etched using the resist mask, so that the conductive layers 405a and 406a can be formed. Note that in that case, the resist mask is removed after the conductive layers 405a and 406a are formed.

[0289] Then, as illustrated in FIG. 8E, the oxide insulating layer 407a is formed so as to be in contact with the oxide semiconductor layer 403a.

[0290] For example, the oxide insulating layer 407a can be formed by formation of a film that can be used for the oxide insulating layer 407a in a rare gas (typically, argon) atmosphere, an oxygen atmosphere, or a mixed atmosphere of a rare gas and oxygen by sputtering. By formation of the oxide insulating layer 407a by sputtering, the decrease in resistance of part of the oxide semiconductor layer 403a that functions as a back channel of the transistor can be prevented. The temperature of the substrate at the time of the formation of the oxide insulating layer 407a is preferably higher than or equal to room temperature and lower than or equal to 300° C.

[0291] Before the formation of the oxide insulating layer 407a, plasma treatment using a gas such as N₂O, N₂, or Ar may be performed so that water or the like adsorbed onto an exposed surface of the oxide semiconductor layer 403a is removed. In the case where the plasma treatment is performed, the oxide insulating layer 407a is preferably formed after the plasma treatment without exposure to air.

[0292] In addition, in the example of the method for forming the transistor illustrated in FIG. 7A, heat treatment is performed at higher than or equal to 400° C. and lower than or equal to 750° C., or higher than or equal to 400° C. and lower than the strain point of the substrate, for example. For example, the heat treatment is performed after the oxide semiconductor film is formed, after part of the oxide semiconductor film is etched, after the second conductive film is formed, after part of the second conductive film is etched, or after the oxide insulating layer 407a is formed.

[0293] Note that a heat treatment apparatus for the heat treatment can be an electric furnace or an apparatus for heating an object by heat conduction or heat radiation from a heater such as a resistance heater. For example, an RTA (rapid thermal annealing) apparatus such as a GRTA (gas rapid thermal annealing) apparatus, or an LRTA (lamp rapid thermal annealing) apparatus can be used. An LRTA apparatus is an apparatus for heating an object by radiation of light (an electromagnetic wave) emitted from a lamp such as a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high pressure sodium lamp, or a high pressure mercury lamp. A GRTA apparatus is an apparatus with which heat treatment is performed using a high-temperature gas. As the high-temperature gas, for example, a rare gas or an inert gas (e.g., nitrogen) which does not react with an object by heat treatment can be used.

[0294] After the heat treatment, a high-purity oxygen gas, a high-purity N₂O gas, or ultra-dry air (with a dew point of -40° C. or lower, preferably -60° C. or lower) may be introduced into the furnace that has been used in the heat treatment while the heating temperature is maintained or decreased. In that case, it is preferable that water, hydrogen, and the like be not contained in the oxygen gas or the N₂O gas. The purity of the oxygen gas or the N₂O gas which is introduced into the heat treatment apparatus is preferably 6N or higher, more preferably 7N or higher. That is, the impurity concentration in the oxygen gas or the N₂O gas is 1 ppm or lower, preferably 0.1 ppm or lower. By the action of the oxygen gas or the N₂O gas, oxygen is supplied to the oxide semiconductor layer 403a, so that the oxide semiconductor layer 403a can be highly purified.

[0295] Further, in addition to the heat treatment, after the oxide insulating layer 407a is formed, heat treatment (preferably at 200 to 400° C., for example, 250 to 350° C.) may be performed in an inert gas atmosphere or an oxygen gas atmosphere.

[0296] Further, oxygen doping treatment using oxygen plasma may be performed after the formation of the insulating layer 402a, after the formation of the oxide semiconductor film, after the formation of the conductive layer serving as a source electrode or a drain electrode, after the formation of the oxide insulating layer, or after the heat treatment. For example, oxygen doping treatment using a high-density plasma of 2.45 GHz may be performed. By the oxygen doping treatment, variations in electrical characteristics of the transistors can be reduced.

[0297] Through the steps, an impurity such as hydrogen, moisture, a hydroxyl group, or hydride (also referred to as a hydrogen compound) is removed from the oxide semiconductor layer 403a and oxygen is supplied to the oxide semiconductor layer 403a. Thus, by the action of the oxygen gas or the N₂O gas, defects caused by oxygen deficiency in the oxide semiconductor layer 403a can be reduced.

[0298] Note that although the example of the method for forming the transistor illustrated in FIG. 7A is described, this embodiment is not limited to this example. For example, as for the components in FIGS. 7B to 7D that have the same designations as the components in FIG. 7A and whose functions are at least partly the same as those of the components in FIG. 7A, the description of the example of the method for forming the transistor illustrated in FIG. 7A can be referred to as appropriate.

[0299] As described with reference to FIGS. 7A to 7D and FIGS. 8A to 8E, the example of the transistor in this embodiment includes a conductive layer functioning as a gate electrode; an insulating layer functioning as a gate insulating layer; an oxide semiconductor layer which includes a channel and overlaps with conductive layer functioning as a gate with the insulating layer functioning as a gate insulating layer provided therebetween; a conductive layer which is electrically connected to the oxide semiconductor layer and functions as one of a source and a drain; and a conductive layer which is electrically connected to the oxide semiconductor layer and functions as the other of the source and the drain.

[0300] The oxide semiconductor layer in which a channel is formed is an oxide semiconductor layer which is made to be intrinsic (i-type) or substantially intrinsic (i-type) by purification. By purification of the oxide semiconductor layer, the carrier concentration in the oxide semiconductor layer can be lower than $1 \times 10^{14}/\text{cm}^3$, preferably lower than $1 \times 10^{12}/\text{cm}^3$, more preferably lower than $1 \times 10^{11}/\text{cm}^3$, so that changes in characteristics due to temperature change can be suppressed. Further, with the above structure, off-state current per micrometer of channel width can be 10 nA (1×10^{-17} A) or less, 1 nA (1×10^{-18} A) or less, 10 pA (1×10^{-20} A) or less, 1 pA (1×10^{-21} A) or less, or 100 pA (1×10^{-22} A) or less. It is preferable that the off-state current of the transistor be as low as possible. The lower limit of the off-state current of the transistor in this embodiment is estimated at about 10^{-30} A/ μm .

[0301] A calculation example of the off-state current of the example of the transistor including an oxide semiconductor

layer in this embodiment, in which leakage current measurement with a circuit for evaluating characteristics is utilized, is described below.

[0302] The leakage current measurement with a circuit for evaluating characteristics is described with reference to FIGS. 9A and 9B. FIGS. 9A and 9B illustrate the circuit for evaluating characteristics.

[0303] First, the structure of the circuit for evaluating characteristics is described with reference to FIG. 9A. FIG. 9A is a circuit diagram illustrating the structure of the circuit for evaluating characteristics.

[0304] The circuit for evaluating characteristics illustrated in FIG. 9A includes a plurality of measurement systems 801. The plurality of measurement systems 801 are connected in parallel. Here, as an example, eight measurement systems 801 are connected in parallel. Plural kinds of measurement can be performed using the plurality of measurement systems 801.

[0305] The measurement system 801 includes a transistor 811, a transistor 812, a capacitor 813, a transistor 814, and a transistor 815.

[0306] Voltage V1 is input to one of a source and a drain of the transistor 811, and voltage Vext_a is input to a gate of the transistor 811. The transistor 811 is a transistor for injecting electrical charge.

[0307] One of a source and a drain of the transistor 812 is connected to the other of the source and the drain of the transistor 811. Voltage V2 is input to the other of the source and the drain of the transistor 812. Voltage Vext_b is input to a gate of the transistor 812. The transistor 812 is a transistor for evaluating leakage current. Note that the leakage current here includes the off-state current of a transistor.

[0308] A first capacitor electrode of the capacitor 813 is connected to the other of the source and the drain of the transistor 811. The voltage V2 is input to a second capacitor electrode of the capacitor 813. Note that here, the voltage V2 is 0 V.

[0309] Voltage V3 is input to one of a source and a drain of the transistor 814. A gate of the transistor 814 is connected to the other of the source and the drain of the transistor 811. Note that a portion where the gate of the transistor 814, the one of the source and the drain of the transistor 811, the other of the source and the drain of the transistor 812, and the first capacitor electrode of the capacitor 813 are connected to each other is referred to as a node A. Note that here, the voltage V3 is 5 V.

[0310] One of a source and a drain of the transistor 815 is connected to the other of the source and the drain of the transistor 814. Voltage V4 is input to the other of the source and the drain of the transistor 815. Voltage Vext_c is input to a gate of the transistor 815. Note that here, the voltage Vext_c is 0.5 V.

[0311] The measurement system 801 outputs the voltage of a portion where the other of the source and the drain of the transistor 814 is connected to the one of the source and the drain of the transistor 815, as output voltage Vout.

[0312] Here, a transistor having a channel length L of 10 μm and a channel width W of 10 μm and including an oxide semiconductor layer is used as an example of the transistor 811. A transistor having a channel length L of 3 μm and a channel width W of 100 μm and including an oxide semiconductor layer is used as an example of each of the transistors 814 and 815. A bottom-gate transistor including

an oxide semiconductor layer in which a source and drain electrodes are on and in contact with the oxide semiconductor layer, a region where the source and drain electrodes overlap with a gate electrode is not provided, and an offset region with a width of 1 μm is provided is used as an example of the transistor 812. Provision of the offset region can reduce parasitic capacitance. Further, as the transistor 812, samples (also referred to as SMP) of six transistors having different channel lengths L and different channel widths W are used (see Table 1).

TABLE 1

	L [μm]	W [μm]
SMP1	1.5	1×10^5
SMP2	3	1×10^5
SMP3	10	1×10^5
SMP4	1.5	1×10^6
SMP5	3	1×10^6
SMP6	10	1×10^6

[0313] By separately providing a transistor for injecting electrical charge and a transistor for evaluating leakage current as illustrated in FIG. 9A, the transistor for evaluating leakage current can be always kept off at the time of electrical charge injection. Without provision of the transistor for injecting electrical charge, the transistor for evaluating leakage current needs to be turned on at the time of electrical charge injection. In that case, if the transistor for evaluating leakage current is an element that takes a long time to turn into a steady off-state from an on state, the measurement takes a long time.

[0314] In addition, by separately providing a transistor for injecting electrical charge and a transistor for evaluating leakage current, each of the transistors can have appropriate size. Further, by making the channel width W of the transistor for evaluating leakage current larger than that of the transistor for injecting electrical charge, the leakage current component of the circuit for evaluating characteristics other than the leakage current of the transistor for evaluating leakage current can be made relatively low. Accordingly, the leakage current of the transistor for evaluating leakage current can be measured with high accuracy. Further, the transistor for evaluating leakage current does not need to be turned on at the time of electrical charge injection; thus, there is no influence of fluctuation in the voltage of the node A caused by part of the electrical charge in the channel formation region of the transistor for evaluating leakage current flowing to the node A.

[0315] In contrast, by making the channel width W of the transistor for injecting electrical charge smaller than that of the transistor for evaluating leakage current, the leakage current of the transistor for injecting electrical charge can be made relatively low. Further, there is small influence of fluctuation in the voltage of the node A caused by part of the electrical charge in the channel formation region flowing to the node A at the time of electrical charge.

[0316] Next, a method for measuring the leakage current of the circuit for evaluating characteristics illustrated in FIG. 9A is described with reference to FIG. 9B. FIG. 9B is a timing chart for describing the method for measuring the leakage current with the use of the circuit for evaluating characteristics illustrated in FIG. 9A.

[0317] In the method for measuring the leakage current with the use of the circuit for evaluating characteristics

illustrated in FIG. 9A, a period is divided into a writing period and a holding period. The operation in each period is described below.

[0318] In the writing period, voltage VL (−3 V) that turns off the transistor 812 is input as the voltage Vext_b. Further, write voltage Vw is input as the voltage V1, and then, voltage VH (5 V) that keeps the transistor 811 on for a certain period is input as the voltage Vext_a. Thus, electrical charge is accumulated in the node A, and the voltage of the node A is equivalent to the write voltage Vw. Then, the voltage VL that turns off the transistor 811 is input as the voltage Vext_a. Then, voltage VSS (0 V) is input as the voltage V1.

[0319] In the holding period, the amount of change in the voltage of the node A due to the change in the amount of electrical charge held in the node A is measured. From the amount of change in voltage, the value of current flowing between the source electrode and the drain electrode of the transistor 812 can be calculated. As described above, electrical charge can be accumulated in the node A, and the amount of change in the voltage of the node A can be measured.

[0320] At this time, accumulation of electrical charge in the node A and measurement of the amount of change in the voltage of the node A (also referred to as accumulation and measurement operation) are repeated. First, first accumulation and measurement operation is repeated 15 times. In the first accumulation and measurement operation, a voltage of 5 V is input as the write voltage Vw in a writing period and is held for 1 h in a holding period. Next, second accumulation and measurement operation is repeated twice. In the second accumulation and measurement operation, a voltage of 3.5 V is input as the write voltage Vw in a writing period and is held for 50 h in a holding period. Then, third accumulation and measurement operation is performed once. In the third accumulation and measurement operation, a voltage of 4.5 V is input as the write voltage Vw in a writing period and is held for 10 h in a holding period. By repeating the accumulation and measurement operation, it can be confirmed that measured current values are values in the steady state. In other words, it is possible to remove transient current (current decreasing over time after the start of the measurement) from I_A (current flowing through the node A). Accordingly, leakage current can be measured with higher accuracy.

[0321] In general, the voltage V_A of the node A is expressed by Formula 1 as a function of the output voltage Vout.

[Formula 1]

$$V_A = F(V_{out}) \quad (1)$$

[0322] In addition, the electrical charge Q_A of the node A is expressed by Formula 2 using the voltage V_A of the node A, capacitance C_A connected to the node A, and a constant (const). Here, the capacitance C_A connected to the node A is the sum of the capacitance of the capacitor 813 and the capacitance components other than the capacitance of the capacitor 813.

[Formula 2]

$$Q_A = C_A V_A + \text{const} \quad (2)$$

[0323] The current I_A of the node A is a time-derivative term of electrical charge flowing to the node A (or electrical charge flowing from the node A), and is thus expressed by Formula 3.

[Formula 3]

$$I_A = \frac{\Delta Q_A}{\Delta t} = \frac{C_A \cdot \Delta F(V_{out})}{\Delta t} \quad (3)$$

[0324] Note that here, as an example, Δt is about 54000 s. The current I_A of the node A, which is leakage current, can be obtained from the capacitance C_A connected to the node A and the output voltage Vout in this manner; thus, the leakage current of the circuit for evaluating characteristics can be obtained.

[0325] Next, measurement results of the output voltage obtained by the measurement method using the circuit for evaluating characteristics, and the leakage current of the circuit for evaluating characteristics that is calculated from the measurement results are described with reference to FIGS. 10A and 10B.

[0326] For example, FIG. 10A illustrates the relationship between the elapsed time Time of the measurement (the first accumulation and measurement operation) and the output voltage Vout in the transistors of SMP4, SMP5, and SMP6. FIG. 10B illustrates the relationship between the elapsed time Time of the measurement and the current I_A calculated by the measurement. FIG. 10A shows that the output voltage Vout fluctuates after the start of the measurement and it takes 10 h or longer for the transistors to go into the steady state.

[0327] FIG. 11 illustrates the relationship between the voltage of the node A and the leakage current in the SMP1 to SMP6 estimated from values obtained in the measurement. In FIG. 11, for example, in the case of SMP4, leakage current is 28 yA/μm when the voltage of the node A is 3.0 V. Since the leakage current includes the off-state current of the transistor 812, the off-state current of the transistor 812 can be considered to be 28 yA/μm or lower.

[0328] FIG. 12, FIG. 13, and FIG. 14 illustrate the relationship between the voltage of the node A and the leakage current in the SMP1 to SMP6 estimated from the measurement at 85° C., 125° C., and 150° C. As illustrated in FIG. 12, FIG. 13, and FIG. 14, even at 150° C., the leakage current is 100 zA/μm or lower.

[0329] As described above, the leakage current of the circuit for evaluating characteristics using a transistor including a highly-purified oxide semiconductor layer serving as a channel formation layer is sufficiently low, which means that the off-state current of the transistor is sufficiently low. In addition, it turns out that the off-state current of the transistor is sufficiently low even when the temperature rises.

Embodiment 8

[0330] In this embodiment, structure examples of the input-output device in the above embodiment are described.

[0331] The input-output device in this embodiment includes a first substrate (an active matrix substrate) provided with a semiconductor element such as a transistor, a second substrate, and a liquid crystal layer provided between the first substrate and the second substrate.

[0332] First, structure examples of the active matrix substrate in this embodiment are described with reference to FIGS. 15A and 15B and FIGS. 16A and 16B. FIGS. 15A and 15B and FIGS. 16A and 16B illustrate structure examples of the active matrix substrate in the input-output device of this embodiment. FIG. 15A is a schematic plan view, and FIG. 15B is a schematic cross-sectional view taken along line A-B in FIG. 15A. FIG. 16A is a schematic plan view, and FIG. 16B is a schematic cross-sectional view taken along line C-D in FIG. 16A. Note that in FIGS. 16A and 16B, a photodetector with the structure of FIG. 4A is used as an example of a photodetector. In FIGS. 15A and 15B and FIGS. 16A and 16B, the transistor with the structure described with reference to FIG. 7A is used as an example of a transistor.

[0333] The active matrix substrate illustrated in FIGS. 15A and 15B and FIGS. 16A and 16B includes a substrate 500, conductive layers 501a to 501h, an insulating layer 502, semiconductor layers 503a to 503d, conductive layers 504a to 504k, an insulating layer 505, a semiconductor layer 506, a semiconductor layer 507, a semiconductor layer 508, an insulating layer 509, and conductive layers 510a to 510c.

[0334] Each of the conductive layers 501a to 501h is formed over one surface of the substrate 500.

[0335] The conductive layer 501a functions as a gate of a display selection transistor in a display circuit.

[0336] The conductive layer 501b functions as a first capacitor electrode of a storage capacitor in the display circuit. Note that a layer that functions as a first capacitor electrode of a capacitor (a storage capacitor) is also referred to as a first capacitor electrode.

[0337] The conductive layer 501c functions as a wiring through which the voltage V_b is input. Note that a layer that functions as a wiring is also referred to as a wiring.

[0338] The conductive layer 501d functions as a gate of a photodetection control transistor in the photodetector.

[0339] The conductive layer 501e functions as a signal line through which a photodetection control signal is input. Note that a layer that functions as a signal line is also referred to as a signal line.

[0340] The conductive layer 501f functions as a gate of an output control transistor in the photodetector.

[0341] The conductive layer 501g functions as a gate of an amplifier transistor in the photodetector.

[0342] The insulating layer 502 is provided over the one surface of the substrate 500 with the conductive layers 501a to 501h provided therebetween.

[0343] The insulating layer 502 functions as a gate insulating layer of the display selection transistor in the display circuit, a dielectric layer of the storage capacitor in the display circuit, a gate insulating layer of the photodetection control transistor in the photodetector, a gate insulating layer of the amplifier transistor in the photodetector, and a gate insulating layer of the output selection transistor in the photodetector.

[0344] The semiconductor layer 503a overlaps with the conductive layer 501a with the insulating layer 502 provided therebetween. The semiconductor layer 503a functions as a channel formation layer of the display selection transistor in the display circuit.

[0345] The semiconductor layer 503b overlaps with the conductive layer 501d with the insulating layer 502 provided

therebetween. The semiconductor layer 503b functions as a channel formation layer of the photodetection control transistor in the photodetector.

[0346] The semiconductor layer 503c overlaps with the conductive layer 501f with the insulating layer 502 provided therebetween. The semiconductor layer 503c functions as a channel formation layer of the output selection transistor in the photodetector.

[0347] The semiconductor layer 503d overlaps with the conductive layer 501g with the insulating layer 502 provided therebetween. The semiconductor layer 503d functions as a channel formation layer of the amplifier transistor in the photodetector.

[0348] The conductive layer 504a is electrically connected to the semiconductor layer 503a. The conductive layer 504a functions as one of a source and, a drain of the display selection transistor in the display circuit.

[0349] The conductive layer 504b is electrically connected to the conductive layer 501b and the semiconductor layer 503a. The conductive layer 504b functions as the other of the source and the drain of the display selection transistor in the display circuit.

[0350] The conductive layer 504c overlaps with the conductive layer 501b with the insulating layer 502 provided therebetween. The conductive layer 504c functions as a second capacitor electrode of the storage capacitor in the display circuit.

[0351] The conductive layer 504d is electrically connected to the conductive layer 501c through an opening that penetrates the insulating layer 502. The conductive layer 504d functions as one of a first current terminal and a second current terminal of a photoelectric conversion element in the photodetector.

[0352] The conductive layer 504e is electrically connected to the semiconductor layer 503b. The conductive layer 504e functions as one of a source and a drain of the photodetection control transistor in the photodetector.

[0353] The conductive layer 504f is electrically connected to the semiconductor layer 503b and is electrically connected to the conductive layer 501g through an opening that penetrates the insulating layer 502. The conductive layer 504f functions as the other of the source and the drain of the photodetection control transistor in the photodetector.

[0354] The conductive layer 504g is electrically connected to the conductive layer 501d and the conductive layer 501e through an opening that penetrates the insulating layer 502. The conductive layer 504g functions as a signal line through which a photodetection control signal is input.

[0355] The conductive layer 504h is electrically connected to the semiconductor layer 503c. The conductive layer 504h functions as one of a source and a drain of the output selection transistor in the photodetector.

[0356] The conductive layer 504i is electrically connected to the semiconductor layer 503c and the semiconductor layer 503d. The conductive layer 504i functions as the other of the source and the drain of the output selection transistor in the photodetector and one of a source and a drain of the amplifier transistor in the photodetector.

[0357] The conductive layer 504j is electrically connected to the semiconductor layer 503d and is electrically connected to the conductive layer 501h through an opening that penetrates the insulating layer 502. The conductive layer 504j functions as the other of the source and the drain of the amplifier transistor in the photodetector.

[0358] The conductive layer 504k is electrically connected to the conductive layer 501h through an opening that penetrates the insulating layer 502. The conductive layer 504k functions as a wiring through which the voltage V_a or the voltage V_b is input.

[0359] The insulating layer 505 is in contact with the semiconductor layers 503a to 503d with the conductive layers 504a to 504k provided therebetween.

[0360] The semiconductor layer 506 is electrically connected to the conductive layer 504d through an opening that penetrates the insulating layer 505.

[0361] The semiconductor layer 507 is in contact with the semiconductor layer 506.

[0362] The semiconductor layer 508 is in contact with the semiconductor layer 507.

[0363] The insulating layer 509 overlaps with the insulating layer 505, the semiconductor layer 506, the semiconductor layer 507, and the semiconductor layer 508. The insulating layer 509 functions as a planarization insulating layer in the display circuit and the photodetector. Note that the insulating layer 509 is not necessarily provided.

[0364] The conductive layer 510a is electrically connected to the conductive layer 504b through an opening that penetrates the insulating layers 505 and 509. The conductive layer 510a functions as a pixel electrode of a display element in the display circuit. Note that a layer that functions as a pixel electrode is also referred to as a pixel electrode.

[0365] The conductive layer 510b is electrically connected to the conductive layer 504c through an opening that penetrates the insulating layers 505 and 509. The conductive layer 510b functions as a wiring through which the voltage V_c is input.

[0366] The conductive layer 510c is electrically connected to the conductive layer 504e through an opening that penetrates the insulating layers 505 and 509 and is electrically connected to the semiconductor layer 508 through an opening that penetrates the insulating layers 505 and 509.

[0367] A structure example of the input-output device in this embodiment is described with reference to FIGS. 17A and 17B. FIGS. 17A and 17B are schematic cross-sectional views illustrating the structure example of the input-output device in this embodiment. FIG. 17A is a schematic cross-sectional view of a display circuit, and FIG. 17B is a schematic cross-sectional view of a photodetector. Note that a display element is a liquid crystal element, for example.

[0368] The input-output device illustrated in FIGS. 17A and 17B includes a substrate 512, a light-blocking layer 513, a coloring layer 514, a coloring layer 515, an insulating layer 516, a conductive layer 517, and a liquid crystal layer 518 in addition to the active matrix substrate illustrated in FIGS. 15A and 15B and FIGS. 16A and 16B.

[0369] The light-blocking layer 513 is provided on part of one surface of the substrate 512.

[0370] The coloring layer 514 is provided on part of the substrate 512 where the light-blocking layer 513 is not provided, and overlaps with the semiconductor layer 506, the semiconductor layer 507, and the semiconductor layer 508.

[0371] The coloring layer 515 overlaps with the coloring layer 514.

[0372] The insulating layer 516 is provided on the one surface of the substrate 512 with the light-blocking layer 513, the coloring layer 514, and the coloring layer 515 provided therebetween.

[0373] The conductive layer 517 is provided on the one surface of the substrate 512.

[0374] The conductive layer 517 functions as a common electrode in the display circuit. Note that in the photodetector, the conductive layer 517 is not necessarily provided.

[0375] The liquid crystal layer 518 is provided between the conductive layer 510a and the conductive layer 517 and overlaps with the semiconductor layer 508 with the insulating layer 509 provided therebetween.

[0376] Note that the conductive layer 510a, the liquid crystal layer 518, and the conductive layer 517 function as a display element in the display circuit.

[0377] Further, the components of the input-output device illustrated in FIGS. 17A and 17B are described.

[0378] As each of the substrate 500 and the substrate 512, it is possible to use a substrate that can be used as the substrate 400a in FIG. 7A.

[0379] As the conductive layers 501a to 501h, it is possible to use a layer of a material that can be used for the conductive layer 401a in FIG. 7A. Alternatively, the conductive layers 501a to 501h may be formed using a stack of layers of materials that can be used for the conductive layer 401a.

[0380] As the insulating layer 502, it is possible to use a layer of a material that can be used for the insulating layer 402a in FIG. 7A. Alternatively, the insulating layer 502 may be formed using a stack of layers of materials that can be used for the insulating layer 402a.

[0381] As the semiconductor layers 503a to 503d, it is possible to use a layer of a material that can be used for the oxide semiconductor layer 403a in FIG. 7A. Note that as the semiconductor layers 503a to 503d, a semiconductor layer using a semiconductor that belongs to Group 14 in the periodic table (e.g., silicon) may be used.

[0382] As the conductive layers 504a to 504k, it is possible to use a layer of a material that can be used for the conductive layer 405a or the conductive layer 406a in FIG. 7A. Alternatively, the conductive layers 504a to 504k may be formed using a stack of layers of materials that can be used for the conductive layer 405a or the conductive layer 406a.

[0383] As the insulating layer 505, it is possible to use a layer of a material that can be used for the oxide insulating layer 407a in FIG. 7A. Alternatively, the insulating layer 505 may be formed using a stack of layers of materials that can be used for the oxide insulating layer 407a.

[0384] The semiconductor layer 506 is a semiconductor layer with one conductivity (one of p-type conductivity or n-type conductivity). As the semiconductor layer 506, a semiconductor layer containing silicon can be used, for example.

[0385] The semiconductor layer 507 has lower resistance than the semiconductor layer 506. As the semiconductor layer 507, a semiconductor layer containing silicon can be used, for example.

[0386] The semiconductor layer 508 is a semiconductor layer whose conductivity is different from the conductivity of the semiconductor layer 506 (the other of the p-type conductivity and the n-type conductivity). As the semiconductor layer 508, a semiconductor layer containing silicon can be used, for example.

[0387] As the insulating layer 509 and the insulating layer 516, for example, a layer of an organic material such as polyimide, acrylic, or benzocyclobutene can be used. Alter-

natively, as the insulating layer **509**, a layer of a low-dielectric constant material (also referred to as a low-k material) can be used.

[0388] As the conductive layers **510a** to **510c** and the conductive layer **517**, for example, a layer of a light-transmitting conductive material such as indium tin oxide, a metal oxide in which zinc oxide is mixed in indium oxide (such a metal oxide is also referred to as indium zinc oxide (IZO)), a conductive material in which silicon oxide (SiO_2) is mixed in indium oxide, organoindium, organotin, indium oxide containing tungsten oxide, indium zinc oxide containing tungsten oxide, indium oxide containing titanium oxide, or indium tin oxide containing titanium oxide can be used.

[0389] The conductive layers **510a** to **510c** and the conductive layer **517** can be formed using a conductive composition containing a conductive high-molecular compound (also referred to as a conductive polymer). A conductive layer formed using the conductive composition preferably has a sheet resistance of 10000 ohm/square or less and a transmittance of 70% or more at a wavelength of 550 nm. Further, the resistivity of the conductive high-molecular compound contained in the conductive composition is preferably 0.1 $\Omega\cdot\text{cm}$ or less.

[0390] As the conductive high-molecular compound, a so-called it electron conjugated conductive high-molecular compound can be used. For example, polyaniline and/or a derivative thereof, polypyrrole and/or a derivative thereof, polythiophene and/or a derivative thereof, and a copolymer of two or more kinds of those materials can be given as the it electron conjugated conductive high-molecular compound.

[0391] As the light-blocking layer **513**, a layer formed using a metal material can be used, for example.

[0392] The coloring layer **514** is one of a red coloring layer and a blue coloring layer.

[0393] The coloring layer **515** is the other of the red coloring layer and the blue coloring layer.

[0394] Note that the stack of the coloring layer **514** and the coloring layer **515** functions as a filter for absorbing visible light.

[0395] The liquid crystal layer **518** can be, for example, a layer containing a TN liquid crystal, an OCB liquid crystal, an STN liquid crystal, a VA liquid crystal, an ECB liquid crystal, a GH liquid crystal, a polymer dispersed liquid crystal, or a discotic liquid crystal can be used. Note that for the liquid crystal layer **518**, a liquid crystal that transmits light when voltage applied to the conductive layer **510c** and the conductive layer **517** is 0 V is preferably used.

[0396] As described with reference to FIGS. **15A** and **15B**, FIGS. **16A** and **16B**, and FIGS. **17A** and **17B**, the structure example of the input-output device in this embodiment includes the active matrix substrate provided with the transistor, the pixel electrode, and the photoelectric conversion element, a counter substrate, and the liquid crystal layer having a liquid crystal between the active matrix substrate and the counter substrate. With such a structure, the display circuit and the photodetector can be manufactured over one substrate in the same steps; thus, manufacturing cost can be reduced.

[0397] As described with reference to FIGS. **17A** and **17B**, the structure example of the input-output device in this embodiment includes the filter that overlaps with the photoelectric conversion element and absorbs visible light. With such a structure, visible light (e.g., light of a light-emitting

diode that emits visible light) can be prevented from entering the photoelectric conversion element, so that accuracy of photodetection in an infrared range can be improved.

Embodiment 9

[0398] In this embodiment, electronic devices each including the input-output device described in the above embodiment are described.

[0399] Structure examples of electronic devices in this embodiment are described with reference to FIGS. **18A** to **18F**. FIGS. **18A** to **18F** illustrate the structure examples of the electronic devices in this embodiment.

[0400] The electronic device illustrated in FIG. **18A** is a personal digital assistant. The personal digital assistant illustrated in FIG. **18A** includes at least an input-output portion **1001**. In the personal digital assistant illustrated in FIG. **18A**, for example, the input-output portion **1001** can be provided with an operation portion **1002**. For example, when the input-output device in the above embodiment is used for the input-output portion **1001**, operation of the personal digital assistant or input of data to the personal digital assistant can be performed with a finger or a pen.

[0401] The electronic device illustrated in FIG. **18B** is an information guide terminal including a car navigation system, for example. The information guide terminal illustrated in FIG. **18B** includes an input-output portion **1101**, operation buttons **1102**, and an external input terminal **1103**. For example, when the input-output device in the above embodiment is used for the input-output portion **1101**, operation of the information guide terminal or input of data to the information guide terminal can be performed with a finger or a pen.

[0402] The electronic device illustrated in FIG. **18C** is a laptop personal computer. The laptop personal computer illustrated in FIG. **18C** includes a housing **1201**, an input-output portion **1202**, a speaker **1203**, an LED lamp **1204**, a pointing device **1205**, a connection terminal **1206**, and a keyboard **1207**. For example, when the input-output device in the above embodiment is used for the input-output portion **1202**, operation of the laptop personal computer or input of data to the laptop personal computer can be performed with a finger or a pen. Further, the input-output device in the above embodiment may be used for the pointing device **1205**.

[0403] The electronic device illustrated in FIG. **18D** is a portable game machine. The portable game machine illustrated in FIG. **18D** includes an input-output portion **1301**, an input-output portion **1302**, a speaker **1303**, a connection terminal **1304**, an LED lamp **1305**, a microphone **1306**, a recording medium read portion **1307**, operation buttons **1308**, and a sensor **1309**. For example, when the input-output device in the above embodiment is used for either one or both the input-output portion **1301** and the input-output portion **1302**, operation of the portable game machine or input of data to the portable game machine can be performed with a finger or a pen.

[0404] The electronic device illustrated in FIG. **18E** is an e-book reader. The e-book reader illustrated in FIG. **18E** includes at least a housing **1401**, a housing **1403**, an input-output portion **1405**, an input-output portion **1407**, and a hinge **1411**.

[0405] The housing **1401** and the housing **1403** are connected to each other with the hinge **1411** so that the e-book reader illustrated in FIG. **18E** can be opened and closed with

the hinge **1411** used as an axis. With such a structure, the e-book reader can operate like a paper book. The input-output portion **1405** and the input-output portion **1407** are incorporated in the housing **1401** and the housing **1403**, respectively. The input-output portion **1405** and the input-output portion **1407** may display different images. For example, one image can be displayed across both the input-output portions. In the case where different images are displayed on the input-output portion **1405** and the input-output portion **1407**, for example, text may be displayed on the input-output portion on the right side (the input-output portion **1405** in FIG. **18E**) and an image may be displayed on the input-output portion on the left side (the input-output portion **1407** in FIG. **18E**).

[0406] In addition, in the e-book reader illustrated in FIG. **18E**, the housing **1401** or the housing **1403** may be provided with an operation portion or the like. For example, the e-book reader illustrated in FIG. **18E** may include a power switch **1421**, operation keys **1423**, and a speaker **1425**. In the e-book reader illustrated in FIG. **18E**, pages of an image with the plurality of pages can be turned with the operation key **1423**. Further, in the e-book reader illustrated in FIG. **18E**, a keyboard, a pointing device, or the like may be provided in either one or both the input-output portion **1405** and the input-output portion **1407**. Furthermore, in the e-book reader illustrated in FIG. **18E**, an external connection terminal (e.g., an earphone terminal, a USB terminal, or a terminal that can be connected to an AC adapter or a variety of cables such as USB cables), a recording medium insertion portion, or the like may be provided on the back surface or side surface of the housing **1401** and the housing **1403**. The e-book reader illustrated in FIG. **18E** may function as an electronic dictionary.

[0407] For example, when the input-output device in the above embodiment is used for either one or both the input-output portion **1405** and the input-output portion **1407**, operation of the e-book reader or input of data to the e-book reader can be performed with a finger or a pen.

[0408] The electronic device illustrated in FIG. **18F** is a display. The display illustrated in FIG. **18F** includes a housing **1501**, an input-output portion **1502**, a speaker **1503**, an LED lamp **1504**, operation buttons **1505**, a connection terminal **1506**, a sensor **1507**, a microphone **1508**, and a support base **1509**. For example, when the input-output device in the above embodiment is used for the input-output portion **1502**, operation of the display or input of data to the display can be performed with a finger or a pen.

[0409] As described with reference to FIGS. **18A** to **18F**, the electronic devices in this embodiment each include an input-output portion in which the input-output device in the above embodiment is used. With such a structure, the influence of light in an environment in which the electronic device is placed can be reduced, so that the accuracy of photodetection in the input-output portion can be improved.

[0410] This application is based on Japanese Patent Application serial No. 2010-137090 filed with Japan Patent Office on Jun. 16, 2010, the entire contents of which are hereby incorporated by reference.

1. (canceled)
2. A display device with an infrared optical sensor comprising:
 - a light unit comprising a first light-emitting diode that emits light with a wavelength in a visible light range

- and a second light-emitting diode that emits light with a wavelength in an infrared range;

- a plurality of display circuits overlapping with the light unit; and

- a plurality of photodetectors overlapping with the light unit,

- wherein the plurality of photodetectors include a filter for absorbing light with a wavelength in a visible light range,

- wherein the second light-emitting diode is configured not to emit light when the first light-emitting diode emits light,

- wherein the plurality of display circuits are configured to receive a display selection signal, to receive a display data signal in accordance with the display selection signal, and to set a display state in accordance with the display data signal, and

- wherein the plurality of photodetectors are configured to generate data based on illuminance of incident light.

3. The display device according to claim 2,

- wherein each of the plurality of photodetectors comprises a first transistor, a second transistor and a photoelectric conversion element,

- wherein one of a source electrode and a drain electrode of the first transistor is electrically connected to the photoelectric conversion element,

- wherein a gate of the second transistor is electrically connected to the other of the source electrode and the drain electrode of the first transistor,

- wherein the photoelectric conversion element comprises a first conductive layer, a semiconductor layer over the first conductive layer and a second conductive layer over the semiconductor layer,

- wherein the semiconductor layer comprises a silicon layer,

- wherein one of the source electrode and the drain electrode of the first transistor is electrically connected to the second conductive layer,

- wherein the first transistor and the second transistor are field effect transistors, and

- wherein the photoelectric conversion element is configured to supply current between the first conductive layer and the second conductive layer in accordance with the illuminance of the incident light.

4. The display device according to claim 3,

- wherein the first transistor comprises an oxide semiconductor layer,

- wherein the source electrode and the drain electrode of the first transistor are over and in contact with the oxide semiconductor layer,

- wherein the oxide semiconductor layer comprises an intrinsic or substantially intrinsic oxide semiconductor, and

- wherein the oxide semiconductor layer has a carrier concentration of lower than $1 \times 10^{14}/\text{cm}^3$.

5. The display device according to claim 2, further comprising:

- a reading circuit configured to read the data based on the illuminance of the incident light supplied from the plurality of photodetectors; and

- a data processing circuit configured to generate difference data between two pieces of data based on the illuminance of the incident light.

6. The display device according to claim 3,
wherein the source electrode, the drain electrode and the first conductive layer are over and in contact with a first insulating layer, and
wherein a second insulating layer is provided so as to be in contact with an oxide semiconductor layer and the first conductive layer.
7. The display device according to claim 3,
wherein an off-state current of the first transistor per micrometer of channel width is between 100 yA and about 10^{-30} A.
8. A display device with an infrared optical sensor comprising:
a first light unit comprising a first light-emitting diode that emits light with a wavelength in a visible light range;
a second light unit comprising a second light-emitting diode that emits light with a wavelength in an infrared range;
a plurality of display circuits provided between the first light unit and the second light unit; and
a plurality of photodetectors provided between the first light unit and the second light unit,
wherein the plurality of photodetectors include a filter for absorbing light with a wavelength in a visible light range,
wherein the second light-emitting diode is configured not to emit light when the first light-emitting diode emits light,
wherein the plurality of display circuits are configured to receive a display selection signal, to receive a display data signal in accordance with the display selection signal, and to set a display state in accordance with the display data signal, and
wherein the plurality of photodetectors are configured to generate data based on illuminance of incident light.
9. The display device according to claim 8,
wherein each of the plurality of photodetectors comprises a first transistor, a second transistor and a photoelectric conversion element,
wherein one of a source electrode and a drain electrode of the first transistor is electrically connected to the photoelectric conversion element,
wherein a gate of the second transistor is electrically connected to the other of the source electrode and the drain electrode of the first transistor,
wherein the photoelectric conversion element comprises a first conductive layer, a semiconductor layer over the first conductive layer and a second conductive layer over the semiconductor layer,
wherein the semiconductor layer comprises a silicon layer,
wherein one of the source electrode and the drain electrode of the first transistor is electrically connected to the second conductive layer,
wherein the first transistor and the second transistor are field effect transistors, and
wherein the photoelectric conversion element is configured to supply current between the first conductive layer and the second conductive layer in accordance with the illuminance of the incident light.
10. The display device according to claim 9,
wherein the first transistor comprises an oxide semiconductor layer,
wherein the source electrode and the drain electrode of the first transistor are over and in contact with the oxide semiconductor layer,
wherein the oxide semiconductor layer comprises an intrinsic or substantially intrinsic oxide semiconductor, and
wherein the oxide semiconductor layer has a carrier concentration of lower than $1 \times 10^{14}/\text{cm}^3$.
11. The display device according to claim 8, further comprising:
a reading circuit configured to read the data based on the illuminance of the incident light supplied from the plurality of photodetectors; and
a data processing circuit configured to generate difference data between two pieces of data based on the illuminance of the incident light.
12. The display device according to claim 9,
wherein the source electrode, the drain electrode and the first conductive layer are over and in contact with a first insulating layer, and
wherein a second insulating layer is provided so as to be in contact with an oxide semiconductor layer and the first conductive layer.
13. The display device according to claim 9,
wherein an off-state current of the first transistor per micrometer of channel width is 100 yA or less and about 10^{-30} A or more.
14. A display device with an infrared optical sensor comprising:
a first light-emitting diode that emits light with a wavelength in a visible light range,
a second light-emitting diode that emits light with a wavelength in an infrared range;
a plurality of display circuits overlapping with the second light-emitting diode; and
a plurality of photodetectors overlapping with the second light-emitting diode,
wherein the plurality of photodetectors include a filter for absorbing light with a wavelength in a visible light range,
wherein the second light-emitting diode is configured not to emit light when the first light-emitting diode emits light,
wherein the plurality of display circuits are configured to receive a display selection signal, to receive a display data signal in accordance with the display selection signal, and to set a display state in accordance with the display data signal, and
wherein the plurality of photodetectors are configured to generate data based on illuminance of incident light.
15. The display device according to claim 14,
wherein each of the plurality of photodetectors comprises a first transistor, a second transistor and a photoelectric conversion element,
wherein one of a source electrode and a drain electrode of the first transistor is electrically connected to the photoelectric conversion element,
wherein a gate of the second transistor is electrically connected to the other of the source electrode and the drain electrode of the first transistor,
wherein the photoelectric conversion element comprises a first conductive layer, a semiconductor layer over the first conductive layer and a second conductive layer over the semiconductor layer,

wherein the semiconductor layer comprises a silicon layer,
wherein one of the source electrode and the drain electrode of the first transistor is electrically connected to the second conductive layer,
wherein the first transistor and the second transistor are field effect transistors, and
wherein the photoelectric conversion element is configured to supply current between the first conductive layer and the second conductive layer in accordance with the illuminance of the incident light.

16. The display device according to claim **15**,
wherein the first transistor comprises an oxide semiconductor layer,
wherein the source electrode and the drain electrode of the first transistor are over and in contact with the oxide semiconductor layer,
wherein the oxide semiconductor layer comprises an intrinsic or substantially intrinsic oxide semiconductor, and
wherein the oxide semiconductor layer has a carrier concentration of lower than $1 \times 10^{14}/\text{cm}^3$.

17. The display device according to claim **14**, further comprising:

a reading circuit configured to read the data based on the illuminance of the incident light supplied from the plurality of photodetectors; and

a data processing circuit configured to generate difference data between two pieces of data based on the illuminance of the incident light.

18. The display device according to claim **15**,

wherein the source electrode, the drain electrode and the first conductive layer are over and in contact with a first insulating layer, and

wherein a second insulating layer is provided so as to be in contact with an oxide semiconductor layer and the first conductive layer.

19. The display device according to claim **15**,

wherein an off-state current of the first transistor per micrometer of channel width is between 100 pA and about 10^{-30} A.

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